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IMAGING DEVICE AND ELECTRONIC DEVICE

Abstract

Provided are an imaging device and an electronic device configured such that deterioration in imaging performance due to high-angle incident light can be inhibited. The imaging device includes: a semiconductor substrate including a plurality of photoelectric conversion elements; a plurality of color filters that are provided on the semiconductor substrate and face each of the plurality of photoelectric conversion elements; and a partition wall that is provided on the semiconductor substrate and provides separation between one color filter and another color filter adjacent to each other among the plurality of color filters. The partition wall includes a first metal layer, a translucent first partition wall layer that covers a side surface of the first metal layer, and a translucent second partition wall layer located between the first metal layer and the first partition wall layer. A refractive index of the second partition wall layer is larger than a refractive index of the first partition wall layer.

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Background/Summary

CROSS REFERENCE TO RELATED APPLICATIONS [0001] This application is a continuation application of U.S. patent application Ser. No. 17/972,781, filed Oct. 25, 2022, which is a continuous application of U.S. patent application Ser. No. 17/756,175, filed May 18, 2022, which is a U.S. National Phase of International Patent Application No. PCT/JP2020/038146 filed on Oct. 8, 2020, which claims priority benefit of Japanese Patent Application No. JP 2019-215174 filed in the Japan Patent Office on Nov. 28, 2019. Each of the above-referenced applications is hereby incorporated herein by reference in its entirety.

TECHNICAL FIELD

[0002] The present disclosure relates to an imaging device and an electronic device.

BACKGROUND ART

[0003] An imaging device used for a digital camera or the like has a plurality of pixels. Each of the plurality of pixels is provided with a photoelectric conversion element that detects light and generates electrical charges. In addition, color filters that allow only light of specific colors to pass therethrough are provided above the plurality of photoelectric conversion elements. In this type of imaging device, a technique of disposing a partition wall between a color filter of one pixel and a color filter of another pixel in order to prevent color mixing from occurring between adjacent pixels is known (see, for example, PTL 1).

CITATION LIST

Patent Literature

[0004] [PTL 1] [0005] JP 2011-71483 A

SUMMARY

Technical Problem

[0006] In the imaging device, when light is obliquely incident on a surface of a color filter, some of the obliquely incident light may be reflected by a partition wall, and the reflected light that should not be incident may be photoelectrically converted in a pixel. For example, when light such as flare light is incident on a surface of a color filter at a high angle, some of the light incident at a high angle (hereinafter referred to as high-angle incident light) passes through the color filter, reaches a partition wall, is reflected by the partition wall, and is incident on a pixel. As a result, the high-angle incident light is photoelectrically converted, and color mixing or the like is caused in a pixel signal, which may deteriorate performance of the imaging device.

[0007] The present disclosure has been made in view of such circumstances, and an object of the present invention is to provide an imaging device and an electronic device configured such that deterioration in imaging performance due to high-angle incident light can be inhibited.

Solution to Problem

[0008] An imaging device according to one aspect of the present disclosure includes: a semiconductor substrate including a plurality of photoelectric conversion elements; a plurality of color filters that are provided on the semiconductor substrate and face each of the plurality of photoelectric conversion elements; and a partition wall that is provided on the semiconductor

substrate and provides separation between one color filter and another color filter adjacent to each other among the plurality of color filters. The partition wall includes a first metal layer, a translucent first partition wall layer that covers a side surface of the first metal layer, and a translucent second partition wall layer located between the first metal layer and the first partition wall layer. A refractive index of the second partition wall layer is larger than a refractive index of the first partition wall layer.

[0009] According to this, the high-angle incident light that is incident on the surface of the color filter at a high angle, such as flare light, passes through the color filter, the first partition wall layer, and the second partition wall layer, and reaches a side surface of the first metal layer. Since the refractive index of the second partition wall layer is larger than the refractive index of the first partition wall layer, the high-angle incident light that has reached the side surface of the first metal layer is attenuated while being repeatedly reflected between the side surface of the first metal layer and the first partition wall layer. Thus, the imaging device can reduce the high-angle incident light that reaches the photoelectric conversion element. The imaging device can inhibit deterioration in imaging performance due to the problem that the high-angle incident light is photoelectrically converted and causes color mixing or the like in a pixel signal.

Description

BRIEF DESCRIPTION OF DRAWINGS

[0010] FIG. 1 is a schematic diagram showing a configuration example of an imaging device according to a first embodiment of the present disclosure.

[0011] FIG. 2 is a cross-sectional view showing a configuration example of a partition wall and a peripheral portion thereof in the imaging device according to the first embodiment of the present disclosure.

[0012] FIG. 3 is a cross-sectional view showing an example of light guiding performed by the partition wall of the imaging device according to the first embodiment of the present disclosure.

[0013] FIG. 4A is a cross-sectional view showing a method for manufacturing the imaging device according to the first embodiment of the present disclosure in the order of processes.

[0014] FIG. 4B is a cross-sectional view showing the method for manufacturing the imaging device according to the first embodiment of the present disclosure in the order of processes.

[0015] FIG. 4C is a cross-sectional view showing the method for manufacturing the imaging device according to the first embodiment of the present disclosure in the order of processes.

[0016] FIG. 4D is a cross-sectional view showing the method for manufacturing of the imaging device according to the first embodiment of the present disclosure in the order of processes.

[0017] FIG. 4E is a cross-sectional view showing the method for manufacturing of the imaging device according to the first embodiment of the present disclosure in the order of processes.

[0018] FIG. 4F is a cross-sectional view showing the method for manufacturing of the imaging device according to the first embodiment of the present disclosure in the order of processes.

[0019] FIG. 4G is a cross-sectional view showing the method for manufacturing of the imaging device according to the first embodiment of the present disclosure in the order of processes.

[0020] FIG. 4H is a cross-sectional view showing the method for manufacturing of the imaging device according to the first embodiment of the present disclosure in the order of processes.

[0021] FIG. 4I is a cross-sectional view showing the method for manufacturing of the imaging device according to the first embodiment of the present disclosure in the order of processes.

[0022] FIG. 4J is a cross-sectional view showing the method for manufacturing the imaging device according to the first embodiment of the present disclosure in the order of processes.

[0023] FIG. 4K is a cross-sectional view showing the method for manufacturing the imaging device according to the first embodiment of the present disclosure in the order of processes.

[0024] FIG. 5 is a graph showing results of evaluating a relationship between an incidence angle on a surface of a color filter, quantum efficiency, and a sensitivity ratio in the imaging device according to the first embodiment of the present disclosure and an imaging device according to a comparative example.

[0025] FIG. 6 is a cross-sectional view showing a configuration of a partition wall and a peripheral portion thereof in an imaging device according to a second embodiment of the present disclosure.

[0026] FIG. 7A is a cross-sectional view showing a method for manufacturing the imaging device according to the second embodiment of the present disclosure in the order of processes.

[0027] FIG. 7B is a cross-sectional view showing the method for manufacturing the imaging device according to the second embodiment of the present disclosure in the order of processes.

[0028] FIG. 8 is a cross-sectional view showing a configuration example of the partition wall and the peripheral portion thereof in the imaging device according to the second embodiment of the present disclosure.

[0029] FIG. 9 is a cross-sectional view for explaining prevention of light reflection from a semiconductor substrate side toward a color filter side in the imaging device according to the second embodiment of the present disclosure.

[0030] FIG. 10A is a cross-sectional view showing a method for manufacturing the imaging device according to a third embodiment of the present disclosure in the order of processes.

[0031] FIG. 10B is a cross-sectional view showing the method for manufacturing the imaging device according to the third embodiment of the present disclosure in the order of processes.

[0032] FIG. 10C is a cross-sectional view showing the method for manufacturing the imaging device according to the third embodiment of the present disclosure in the order of processes.

[0033] FIG. 10D is a cross-sectional view showing the method for manufacturing the imaging device according to the third embodiment of the present disclosure in the order of processes.

[0034] FIG. 10E is a cross-sectional view showing the method for manufacturing the imaging device according to the third embodiment of the present disclosure in the order of processes.

[0035] FIG. 11 is a cross-sectional view showing a configuration example of a partition wall and a peripheral portion thereof in an imaging device according to a fourth embodiment of the present disclosure.

[0036] FIG. 12 is a cross-sectional view for explaining light shielding from a partition wall side to a semiconductor substrate side in the imaging device according to the fourth embodiment of the present disclosure.

[0037] FIG. 13A is a cross-sectional view showing a method for manufacturing the imaging device according to the fourth embodiment of the present disclosure in the order of processes.

[0038] FIG. 13B is a cross-sectional view showing the method for manufacturing the imaging device according to the fourth embodiment of the present disclosure in the order of processes.

[0039] FIG. 13C is a cross-sectional view showing the method for manufacturing the imaging device according to the fourth embodiment of the present disclosure in the order of processes.

[0040] FIG. 13D is a cross-sectional view showing the method for manufacturing the imaging device according to the fourth embodiment of the present disclosure in the order of processes.

[0041] FIG. 13E is a cross-sectional view showing the method for manufacturing the imaging device according to the fourth embodiment of the present disclosure in the order of processes.

[0042] FIG. 13F is a cross-sectional view showing the method for manufacturing the imaging device according to the fourth embodiment of the present disclosure in the order of processes.

[0043] FIG. 13G is a cross-sectional view showing the method for manufacturing the imaging device according to the fourth embodiment of the present disclosure in the order of processes.

[0044] FIG. 13H is a cross-sectional view showing the method for manufacturing the imaging device according to the fourth embodiment of the present disclosure in the order of processes.

[0045] FIG. 14 is a cross-sectional view showing a configuration example of a partition wall and a peripheral portion thereof in an imaging device according to a fifth embodiment of the present

disclosure.

[0046] FIG. **15A** is a cross-sectional view showing a method for manufacturing the imaging device according to the fifth embodiment of the present disclosure in the order of processes.

[0047] FIG. **15B** is a cross-sectional view showing the method for manufacturing the imaging device according to the fifth embodiment of the present disclosure in the order of processes.

[0048] FIG. **16** is a cross-sectional view showing a configuration example of a partition wall and a peripheral portion thereof in an imaging device according to a sixth embodiment of the present disclosure.

[0049] FIG. **17** is a diagram illustrating a central region and a peripheral region of an imaging region configured of a plurality of photodiodes in an imaging device according to a seventh embodiment of the present disclosure.

[0050] FIG. **18** shows the imaging device according to the seventh embodiment of the present disclosure and is a cross-sectional view showing a configuration example of a partition wall and a peripheral portion thereof in a peripheral region of an imaging region.

[0051] FIG. **19** is a cross-sectional view showing a configuration example of a partition wall and a peripheral portion thereof in an imaging device according to an eighth embodiment of the present disclosure.

[0052] FIG. **20A** is a cross-sectional view showing a method for manufacturing the imaging device according to the eighth embodiment of the present disclosure in the order of processes.

[0053] FIG. **20B** is a cross-sectional view showing the method for manufacturing the imaging device according to the eighth embodiment of the present disclosure in the order of processes.

[0054] FIG. **20C** is a cross-sectional view showing the method for manufacturing the imaging device according to the eighth embodiment of the present disclosure in the order of processes.

[0055] FIG. **20D** is a cross-sectional view showing the method for manufacturing the imaging device according to the eighth embodiment of the present disclosure in the order of processes.

[0056] FIG. **20E** is a cross-sectional view showing the method for manufacturing the imaging device according to the eighth embodiment of the present disclosure in the order of processes.

[0057] FIG. **20F** is a cross-sectional view showing the method for manufacturing the imaging device according to the eighth embodiment of the present disclosure in the order of processes.

[0058] FIG. **20G** is a cross-sectional view showing the method for manufacturing the imaging device according to the eighth embodiment of the present disclosure in the order of processes.

[0059] FIG. **21** is a cross-sectional view showing a configuration example of a partition wall and a peripheral portion thereof in an imaging device according to a ninth embodiment of the present disclosure.

[0060] FIG. **22A** is a cross-sectional view showing a method for manufacturing the imaging device according to the ninth embodiment of the present disclosure in the order of processes.

[0061] FIG. **22B** is a cross-sectional view showing the method for manufacturing the imaging device according to the ninth embodiment of the present disclosure in the order of processes.

[0062] FIG. **22C** is a cross-sectional view showing the method for manufacturing the imaging device according to the ninth embodiment of the present disclosure in the order of processes.

[0063] FIG. **22D** is a cross-sectional view showing the method for manufacturing the imaging device according to the ninth embodiment of the present disclosure in the order of processes.

[0064] FIG. **22E** is a cross-sectional view showing the method for manufacturing the imaging device according to the ninth embodiment of the present disclosure in the order of processes.

[0065] FIG. **22F** is a cross-sectional view showing the method for manufacturing the imaging device according to the ninth embodiment of the present disclosure in the order of processes.

[0066] FIG. **22G** is a cross-sectional view showing the method for manufacturing the imaging device according to the ninth embodiment of the present disclosure in the order of processes.

[0067] FIG. **22H** is a cross-sectional view showing the method for manufacturing the imaging device according to the ninth embodiment of the present disclosure in the order of processes.

[0068] FIG. 22I is a cross-sectional view showing the method for manufacturing the imaging device according to the ninth embodiment of the present disclosure in the order of processes.

[0069] FIG. 22J is a cross-sectional view showing the method for manufacturing the imaging device according to the ninth embodiment of the present disclosure in the order of processes.

[0070] FIG. 22K is a cross-sectional view showing the method for manufacturing the imaging device according to the ninth embodiment of the present disclosure in the order of processes.

[0071] FIG. 22L is a cross-sectional view showing the method for manufacturing the imaging device according to the ninth embodiment of the present disclosure in the order of processes.

[0072] FIG. 23 is a conceptual diagram showing an example in which the technique according to the present disclosure (the present technique) is applied to an electronic device.

[0073] FIG. 24 is a diagram showing an example of a schematic configuration of an endoscopic surgery system to which the technique according to the present disclosure (the present technique) may be applied.

[0074] FIG. 25 is a block diagram showing an example of a functional configuration of a camera head and a CCU shown in FIG. 24.

[0075] FIG. 26 is a block diagram showing a schematic configuration example of a mobile object control system that is an example of a vehicle control system to which the technique according to the present disclosure may be applied.

[0076] FIG. 27 is a diagram showing an example of an installation position of an imaging unit.

DESCRIPTION OF EMBODIMENTS

[0077] Embodiments of the present disclosure will be described below with reference to the figures. In descriptions of the figures referring to in the following description, the same or similar portions will be denoted by the same or similar reference signs. However, it should be noted that the figures are schematic and relationships between thicknesses and planar dimensions, ratios of thicknesses of respective layers, and the like are different from actual ones. Accordingly, specific thicknesses and dimensions should be determined by taking the following description into consideration. In addition, it goes without saying that the figures also include portions having different dimensional relationships and ratios from each other.

[0078] In addition, it is to be understood that definitions of directions such as upward and downward in the following description are merely definitions provided for the sake of brevity and are not intended to limit technical ideas of the present disclosure. For example, it is obvious that when an object is observed after being rotated by 90°, upward and downward are converted into and interpreted as leftward and rightward, and when an object is observed after being rotated by 180°, upward and downward are interpreted as being inverted.

First Embodiment

(Overall Structure)

[0079] FIG. 1 is a diagram showing a configuration example of an imaging device **100** according to a first embodiment of the present disclosure. The imaging device **100** shown in FIG. 1 is, for example, a CMOS solid-state imaging device. As shown in FIG. 1, the imaging device **100** is configured to have a pixel region (a so-called imaging region) **3**, in which pixels **102** including a plurality of photoelectric conversion elements are regularly arranged two-dimensionally, and a peripheral circuit portion on a semiconductor substrate **111** (for example, a silicon substrate). The pixel **102** is configured to have a photodiode serving as a photoelectric conversion element, and a plurality of pixel transistors (so-called MOS transistors). The plurality of pixel transistors can be configured of three transistors, including a transfer transistor, a reset transistor, and an amplification transistor. The plurality of pixel transistors can also be configured of four transistors by adding a selection transistor to the above three transistors. Since an equivalent circuit of a unit pixel is the same as usual, detailed description thereof will be omitted. The pixel **102** may also have a shared pixel structure. The shared pixel structure is configured of a plurality of photodiodes, a plurality of transfer transistors, one shared floating diffusion, and one other shared pixel transistor.

[0080] The peripheral circuit portion includes a vertical drive circuit **104**, column signal processing circuits **105**, a horizontal drive circuit **106**, an output circuit **107**, a control circuit **108**, and the like. [0081] The control circuit **108** receives input clocks and data instructing an operation mode and the like and outputs data such as internal information of the solid-state imaging device. That is, the control circuit **108** generates clock signals and control signals serving as references for operations of the vertical drive circuit **104**, the column signal processing circuits **105**, the horizontal drive circuit **106**, and the like on the basis of vertical sync signals, horizontal sync signals and master clocks. In addition, the control circuit **108** inputs these signals to the vertical drive circuit **104**, the column signal processing circuits **105**, the horizontal drive circuit **106**, and the like.

[0082] The vertical drive circuit **104** is configured of, for example, a shift register, selects a pixel drive wiring, supplies pulses for driving pixels to the selected pixel drive wiring, and drives the pixels for each row. That is, the vertical drive circuit **104** sequentially selects and scans the pixels **102** in the pixel region **103** in the vertical direction for each row and supplies pixel signals based on signal charges generated in accordance with an amount of light received in the photoelectric conversion element of each of the pixels **102** to the column signal processing circuits **105** through vertical signal lines **109**.

[0083] The column signal processing circuits **105** are disposed, for example, for each column of the pixels **102** and perform signal processing such as noise reduction of signals output from the pixels **102** in one row for each pixel row. That is, the column signal processing circuits **105** perform signal processing such as CDS for removing fixed pattern noise unique to the pixels **102**, signal amplification, and AD conversion. Horizontal selection switches (not shown) are provided at output stages of the column signal processing circuits **105** to be connected between the output stages and the horizontal signal line **110**.

[0084] The horizontal drive circuit **106** is configured of, for example, a shift register, sequentially selects each of the column signal processing circuits **105** by sequentially outputting horizontal scan pulses, and outputs pixel signals from each of the column signal processing circuits **105** to the horizontal signal line **110**.

[0085] The output circuit **107** performs signal processing on signals sequentially supplied from each of the column signal processing circuits **105** through the horizontal signal line **110** and outputs the signals. For example, the output circuit **107** may only perform buffering, or may perform black level adjustment, column variation correction, various digital signal processing, and the like. Input and output terminals **112** exchange signals with the outside.

(Structures of Partition Wall and Peripheral Portion Thereof)

[0086] FIG. **2** is a cross-sectional view showing a configuration example of a partition wall **2** and a peripheral portion thereof in the imaging device **100** according to the first embodiment of the present disclosure. The imaging device **100** has, for example, a back surface light receiving type pixel structure in which incident light is caused to enter from a back surface side of a semiconductor substrate **111**. As shown in FIG. **2**, a plurality of photodiode PDs are provided on a back surface (hereinafter, a light receiving surface) **111a** side of the semiconductor substrate **111**. Further, a translucent insulating film **11** is provided on the light receiving surface **111a** of the semiconductor substrate **111**. The insulating film **11** is, for example, a silicon oxide film (SiO₂).

[0087] The semiconductor substrate **111** is a silicon layer formed by polishing a silicon wafer by chemical mechanical polishing (CMP). A thickness of the semiconductor substrate **111** may be arbitrarily set in accordance with a wavelength of received light. As an example, the thickness of the semiconductor substrate **111** is 5 μm or more and 15 μm or less when visible light is received, 15 μm or more and 50 μm or less when infrared light is received, and 3 μm or more and 7 μm or less when ultraviolet light is received.

[0088] A plurality of color filter CFs are provided on the light receiving surface **111a** of the semiconductor substrate **111** via the insulating film **11**. The plurality of color filter CFs include, for

example, color filters CF1 to CF3. The color filters CF1 to CF3 are colored blue (B), green (G), or red (R), respectively. The color filters CF1 to CF3 are disposed at positions at which they respectively face photodiodes PD1 to PD3 via the insulating film 11.

[0089] Although not shown, the plurality of color filter CFs include a color filter CF4 disposed at a position adjacent to at least one or more of the color filters CF1 to CF3. The color filter CF4 may be colored in any one of blue (B), green (G), and red (R), or may be colored in another color other than these. The color filter CF4 is disposed at a position at which it faces a photodiode PD4 via the insulating film 11. In the following, in a case in which it is not necessary to distinguish the color filters CF1 and CF4 from each other, an identification number at the end of the CF serving as a reference sign will be omitted.

[0090] Also, partition walls 2 are provided on the light receiving surface 111a of the semiconductor substrate 111 via the insulating film 11. A plurality of color filter CFs are separated from each other by the partition walls 2. Further, a plurality of micro lenses ML (an example of the “lens” of the present disclosure) are provided on a side opposite to the semiconductor substrate 111 with the plurality of color filter CFs interposed therebetween. One micro lens ML is disposed on one color filter CF. End portions MLEs of the plurality of micro lenses ML are connected to each other. The end portions MLE of the micro lenses ML are disposed on the partition walls 2.

[0091] The partition wall 2 has a first metal layer 20 located at a central portion of the partition wall 2, a first translucent partition wall layer 21 that covers the first metal layer 20 from an outer side thereof, and a second translucent partition wall layer 22 located between the first metal layer 20 and the first partition wall layer 21. For example, the first metal layer 20 has a first side surface 20a and a second side surface 20b that face the color filters CF in a horizontal direction parallel to the light receiving surface 111a of the semiconductor substrate 111, and an upper end surface 20c (an example of the “end surface” of the present disclosure) that faces the end portion of the micro lens ML in a direction orthogonal to the horizontal direction. The second side surface 20b is located on a side opposite to the first side surface 20a. The upper end surface 20c is located on the micro lens side.

[0092] The second partition wall layer 22 covers the first side surface 20a, the second side surface 20b, and the upper end surface 20c of the first metal layer 20. The first partition wall layer 21 covers the first side surface 20a, the second side surface 20b, and the upper end surface 20c of the first metal layer 20 via the second partition wall layer 22.

[0093] The first metal layer 20 is made of, for example, copper (Cu) or tungsten (W). The first partition wall layer 21 and the second partition wall layer 22 are each configured of a translucent film through which light (for example, at least one type of light of visible light, infrared light, and ultraviolet light) received by the pixels 102 can pass. For example, the first partition wall layer 21 is made of a silicon oxide film (SiO.sub.2). The second partition wall layer 22 is made of a silicon carbide film (a-SiC) having an amorphous crystal structure.

[0094] In the present embodiment, a refractive index n_{22} of the second partition wall layer 22 is larger than a refractive index n_{21} of the first partition wall layer 21 ($n_{22} > n_{21}$). Also, a refractive index n_{cf} of the color filter CF is larger than the refractive index n_{21} of the first partition wall layer 21 ($n_{cf} > n_{21}$). For example, a refractive index of a-SiC used for the second partition wall layer 22 is 2.6. A refractive index of SiO.sub.2 used for the first partition wall layer 21 is 1.46. A refractive index of the color filter CF is 1.68.

(Example of Light Guidance Performed by Partition Wall)

[0095] FIG. 3 is a cross-sectional view showing an example of light guiding performed by the partition wall of the imaging device according to the first embodiment of the present disclosure. As shown in FIG. 3, a case in which light L1 is obliquely incident on a surface of the color filter CF through the micro lens ML, and the incident light L1 reaches a surface of the first partition wall layer 21 of the partition wall 2 is assumed.

[0096] An incidence angle on the surface of the color filter CF is defined as θ_1 , and an incidence

angle on the surface of the first partition wall layer **21** is defined as θ_2 . The incidence angles θ_1 and θ_2 have a relationship of, for example, $\theta_1 = 90^\circ - \theta_2$.

[0097] As described above, the refractive index n_{cf} of the color filter CF is larger than the refractive index n_{21} of the first partition wall layer **21** ($n_{cf} > n_{21}$). For this reason, in a case in which the incidence angle θ_1 of the light L1 on the surface of the color filter CF is a low angle and the incidence angle θ_2 on the surface of the first partition wall layer **21** is equal to or greater than a critical angle, the light L1 is totally reflected on the surface of the first partition wall layer **21**. The critical angle is the smallest incidence angle at which total reflection occurs when light travels from a medium with a high refractive index to a medium with a low refractive index. The light L2 totally reflected by the first partition wall layer **21** travels toward the light receiving surface **111a** side of the semiconductor substrate **111** provided with the photodiode PD.

[0098] On the other hand, in a case in which the incidence angle θ_1 of the light L1 on the surface of the color filter CF is a high angle (that is, the light L1 is a high-angle incident light) and the incidence angle θ_2 on the surface of the first partition wall layer **21** is less than the critical angle, the light L1 is incident on the first partition wall layer **21** except for a part thereof. Light L3 incident on the first partition wall layer **21** passes through the first partition wall layer **21** and the second partition wall layer **22** except for a part thereof, reaches a side surface of the first metal layer **20** (for example, the first side surface **20a**), and is reflected on the side surface of the first metal layer **20**. The light L3 reflected on the side surface of the first metal layer **20** passes through the second partition wall layer **22** and reaches the first partition wall layer **21**.

[0099] As described above, the refractive index n_{22} of the second partition wall layer **22** is larger than the refractive index n_{21} of the first partition wall layer **21** ($n_{21} < n_{22}$). In addition, the light L3 is obliquely incident on the first partition wall layer **21**. For this reason, the light L3 that has reached the first partition wall layer **21** is reflected again to the second partition wall layer **22** side except for a part thereof. For example, in a case in which an incidence angle θ_3 of the light L3 on the first partition wall layer **21** is equal to or greater than the critical angle, the light L3 is totally reflected by the first partition wall layer **21**. The light L3 is repeatedly reflected between the first metal layer **20** and the first partition wall layer **21** and is confined in the second partition wall layer **22**. Intensity of the light L3 confined in the second partition wall layer **22** is attenuated each time the light L3 is reflected by the side surface of the first metal layer **20**.

[0100] In this way, the light L3 is attenuated while repeating the reflection between the first metal layer **20** and the first partition wall layer **21**. Thus, the imaging device **100** can prevent the high-angle incident light (for example, flare light) from reaching the light receiving surface **111a** of the semiconductor substrate **111**. The imaging device **100** can reduce the flare light that reaches the photodiode PD.

[0101] Further, as shown in FIG. 3, each of the light L1 and L2 reaches the photodiode PD and is photoelectrically converted, but a part thereof is reflected by a surface of the insulating film **11** and the light receiving surface **111a** before reaching the photodiode PD. At least a part of the reflected light L4 is incident on the partition wall **2** in the same manner as the above-mentioned light L3 and is attenuated while repeating the reflection between the side surface of the first metal layer **20** (for example, the second side surface **20b**) and the first partition wall layer **21**. Thus, the imaging device **100** can inhibit the light L4 reflected in one pixel **102** from leaking to another pixel **102** through the partition wall **2**.

[0102] Next, a method for manufacturing the imaging device **100** shown in FIG. 2 will be described. The imaging device **100** is manufactured by using various devices such as a film forming device (including a chemical vapor deposition (CVD) device, a sputtering device, and a thermal oxidation device), an exposure device, an etching device, a chemical mechanical polishing (CMP) device, and a bonding device. Hereinafter, these devices are collectively referred to as a manufacturing device. The partition wall **2** of the imaging device **100** and a peripheral portion thereof can be manufactured by a manufacturing method described below.

[0103] FIGS. 4A, 4B, 4C, 4D, 4E, 4F, 4G, 4H, 4I, 4J, and 4K are cross-sectional views showing a method for manufacturing the imaging device according to the first embodiment of the present disclosure in the order of processes. As shown in FIG. 4A, the manufacturing device forms the insulating film **11** on the light receiving surface **111a** of the semiconductor substrate **111** on which the photodiode PD has been formed. For example, the insulating film **11** is a silicon oxide film (SiO₂), and a forming method thereof is a thermal oxidation or CVD method of the semiconductor substrate **111**. Next, the manufacturing device forms a metal layer **20'** on the insulating film **11**. For example, the metal layer **20'** is a thin film of copper (Cu) or tungsten (W), and a forming method thereof is a vapor deposition or sputtering method.

[0104] Next, as shown in FIG. 4B, the manufacturing device forms a resist pattern RP1 on the metal layer **20'**. The resist pattern RP1 has a shape that covers a region serving as the first metal layer **20** (see FIG. 2) of the partition wall **2** and exposes other regions. Next, the manufacturing device dry-etches the metal layer **20'** using the resist pattern RP1 as a mask. Thus, as shown in FIG. 4C, the first metal layer **20** is formed. Next, as shown in FIG. 4D, the manufacturing device removes the resist pattern RP1.

[0105] Next, as shown in FIG. 4E, the manufacturing device forms a translucent insulating layer **22'** above the light receiving surface **111a**. For example, the insulating layer **22'** is a silicon carbide film (a-SiC) having an amorphous crystal structure, and a forming method thereof is a CVD method. The insulating film **11** and the first side surface **20a**, the second side surface **20b**, and the upper end surface **20c** of the first metal layer **20** are covered with the insulating layer **22'**.

[0106] Next, as shown in FIG. 4F, the manufacturing device forms a resist pattern RP2 on the insulating layer **22'**. The resist pattern RP2 has a shape that covers the region serving as the first metal layer **20** and the second partition wall layer **22** (see FIG. 2) of the partition wall **2** and exposes other regions. Next, the manufacturing device dry-etches the insulating layer **22'** using the resist pattern RP2 as a mask. Dry etching is, for example, reactive ion etching (RIE). Thus, as shown in FIG. 4G, the second partition wall layer **22** is formed. After that, the manufacturing device removes the resist pattern RP2.

[0107] Next, as shown in FIG. 4H, the manufacturing device forms a translucent insulating layer **21'** above the light receiving surface **111a**. For example, the insulating layer **21'** is a silicon oxide film (SiO₂), and a forming method thereof is a CVD method. The insulating film **11** and the second partition wall layer **22** are each covered with the insulating layer **21'**.

[0108] Next, the manufacturing device forms a resist pattern (not shown) on the insulating layer **21'**. This resist pattern has a shape that covers the region serving as the first partition wall layer **21** (see FIG. 2) of the partition wall **2** and exposes other regions. Next, the manufacturing device dry-etches the insulating layer **21'** using the resist pattern as a mask. Dry etching is, for example, RIE. Thus, as shown in FIG. 4I, the second partition wall layer **22** is formed. The partition wall **2** having the first metal layer **20**, the first partition wall layer **21**, and the second partition wall layer **22** is finally formed. After that, the manufacturing device removes the resist pattern RP2.

[0109] Next, as shown in FIG. 4J, the manufacturing device forms the color filters CFs in regions between adjacent partition walls **20** (that is, above the photodiode PD). The manufacturing device uses lithography technology to create the color filters CFs for each color. For example, the manufacturing device forms a blue (B) color filter CF1 above the photodiode PD1. Next, the manufacturing device forms a green (G) color filter CF2 above the photodiode PD2. Next, the manufacturing device forms a red (R) color filter CF3 above the photodiode PD3. Each of the color filters CF1 to CF3 is formed such that its bottom surface is in contact with an upper surface of the insulating film **11**, its side surface is in contact with the partition wall **2**, and its upper surface is at the same height as the partition wall **2**.

[0110] Next, as shown in FIG. 4K, the manufacturing device forms the micro lens ML above each of the plurality of color filters CFs. The micro lens ML is a convex lens having a curved upper surface and is made of a film through which light passes. The manufacturing device forms a resin

film on the color filters CFs, heats and melts the formed resin film, and rounds a shape of an upper surface of the melted resin film, thereby forming the micro lenses MLs. The imaging device **100** shown in FIG. **2** is finally formed through the above processes.

(Evaluation Results)

[0111] FIG. **5** is a graph showing results of evaluating a relationship between the incidence angle $\theta 1$ on the surface of the color filter CF (see FIG. **3**), quantum efficiency, and a sensitivity ratio in the imaging device according to the first embodiment of the present disclosure and an imaging device according to a comparative example. The horizontal axis in FIG. **5** indicates the incidence angle $\theta 1$. The vertical axis on a left side in FIG. **5** shows the quantum efficiency (QE) for green light. In addition, the vertical axis on a right side in FIG. **5** shows the sensitivity ratio for green light. The sensitivity ratio is represented by a ratio of quantum efficiency of the first embodiment to quantum efficiency of the comparative example. In addition, the first embodiment is different from the comparative example in a structure of the partition wall. A partition wall of the comparative example has a configuration in which the second partition wall layer **22** is removed from the partition wall of the first embodiment.

[0112] As shown in FIG. **5**, in the range in which the incidence angle $\theta 1$ is small, for example, $\theta 1 \leq 20^\circ$, there is no significant difference in quantum efficiency (QE) between the first embodiment and the conventional example. On the other hand, in the range in which the incidence angle $\theta 1$ is large, for example, $\theta 1 \geq 60^\circ$, the quantum efficiency of the first embodiment is lower than the quantum efficiency of the comparative example, and the sensitivity ratio is lowered. It was confirmed that the imaging device according to the first embodiment has the same sensitivity as the imaging device according to the comparative example for low-angle incident light and can be less sensitive to high-angle incident light than the imaging device according to the comparative example.

[0113] As described above, the imaging device **100** according to one aspect of the present disclosure includes the semiconductor substrate **111** having the plurality of photodiodes PDs, the plurality of color filters CFs that are provided on the semiconductor substrate **111** and respectively face the plurality of photodiodes PDs, and the partition wall **2** that is provided on the semiconductor substrate **111** and provides separation between one color filter CF and another color filter CF adjacent to each other among the plurality of color filters CFs. The partition wall **2** has the first metal layer **20**, the first translucent partition wall layer **21** that covers the side surface of the first metal layer **20**, and the second translucent partition wall layer **22** located between the first metal layer **20** and the first partition wall layer **21**. The refractive index of the second partition wall layer **22** is larger than the refractive index of the first partition wall layer **21**.

[0114] According to this, high-angle incident light, such as flare light, that is incident on the surface of the color filter CF at a high angle passes through the color filter CF, the first partition wall layer **21**, and the second partition wall layer **22** and reaches the side surface of the first metal layer **20**. Since the refractive index of the second partition wall layer **22** is larger than the refractive index of the first partition wall layer **21**, the high-angle incident light that has reached the side surface of the first metal layer **20** is attenuated while being repeatedly reflected between the side surface of the first metal layer **20** and the first partition wall layer **21**. Thus, the imaging device **100** can reduce the high-angle incident light that reaches the photodiode PD. The imaging device **100** can inhibit deterioration in imaging performance due to the problem that the high-angle incident light is photoelectrically converted and causes color mixing or the like in a pixel signal.

Second Embodiment

[0115] In the first embodiment described above, the upper end surface **20c** of the first metal layer **20** is covered with the second partition wall layer **22** and the first partition wall layer **21**. However, in the embodiments of the present disclosure, the structure of the partition wall is not limited thereto. At least one of the second partition wall layer **22** and the first partition wall layer **21** may not be present on the upper end surface **20c** of the first metal layer **20**.

[0116] FIG. 6 is a cross-sectional view showing a configuration of a partition wall 2 and a peripheral portion thereof in an imaging device 100A according to a second embodiment of the present disclosure. As shown in FIG. 6, in the partition wall 2 of the imaging device 100A, the upper end surface 20c of the first metal layer 20 is exposed from the first partition wall layer 21 and the second partition wall layer 22. In addition, the upper end surface 20c of the first metal layer 20 is in contact with the micro lens ML.

[0117] In the imaging device 100A, the high-angle incident light that has reached the side surface of the first metal layer 20 is also attenuated while being repeatedly reflected between the side surface of the first metal layer 20 and the first partition wall layer 21. Accordingly, the imaging device 100A can reduce the high-angle incident light that reaches the photodiode PD. The imaging device 100A can inhibit deterioration in imaging performance due to the problem that high-angle incident light is photoelectrically converted and causes color mixing or the like in a pixel signal.

[0118] Next, a method for manufacturing the imaging device 100A shown in FIG. 6 will be described. FIGS. 7A and 7B are cross-sectional views showing the method for manufacturing the imaging device 100A according to the second embodiment of the present disclosure in the order of processes. In FIG. 7A, processes up to the process of forming the insulating layer 21' are the same as those in the method for manufacturing the imaging device 100 described above. After the insulating layer 21' is formed, as shown in FIG. 7B, the manufacturing device performs a CMP treatment to the surface of the insulating layer 21' to expose the upper end surface 20c of the first metal layer 20. Through the CMP treatment, the upper end surface 20c of the first metal layer 20 becomes flush with or substantially flush with an upper surface of the insulating layer 21'.

[0119] The subsequent processes are the same as those in the method for manufacturing the imaging device 100 described in the first embodiment. The manufacturing device dry-etches the insulating layer 21' using a resist pattern as a mask and forms the first partition wall layer 21 (see FIG. 4I). Next, the manufacturing device forms the color filters CFs (see FIG. 4J) and the micro lenses MLs (see FIG. 4K). Through the above processes, the imaging device 100A shown in FIG. 6 is finally formed.

Third Embodiment

[0120] In the first embodiment, an aspect in which only the insulating film 11 is disposed between the semiconductor substrate 111 and the color filters CFs has been shown. However, in the embodiments of the present disclosure, a structure between the semiconductor substrate 111 and the color filters CFs is not limited thereto. An antireflection film may be disposed between the semiconductor substrate 111 and the color filters CFs. Also, at least one of the first partition wall layer 21 and the second partition wall layer 22 may be used for the antireflection film.

[0121] FIG. 8 is a cross-sectional view showing a configuration example of a partition wall 2 and a peripheral portion thereof in an imaging device 100B according to the second embodiment of the present disclosure. As shown in FIG. 8, in the imaging device 100B, the first partition wall layer 21 and the second partition wall layer 22 are provided between the semiconductor substrate 111 and the color filters CFs. For example, the insulating film 11, the second partition wall layer 22, the first partition wall layer 21, and the color filters CFs are laminated in order above the photodiodes PDs. The second partition wall layer 22 and the first partition wall layer 21 disposed between the semiconductor substrate 111 and the color filters CFs function as antireflection films for preventing light from being reflected from the semiconductor substrate 111 side to the color filter CF side.

[0122] FIG. 9 is a cross-sectional view for explaining prevention of light reflection from the semiconductor substrate 111 side to the color filter CF side in the imaging device 100B according to the second embodiment of the present disclosure. In FIG. 9, a color filter (not shown) is disposed on the first partition wall layer 21. A case in which light L11 that has passed through the color filter is incident on a surface of the first partition wall layer 21 located above the photodiode PD substantially vertically is assumed.

[0123] The light L11 that has passed through the first partition wall layer 21 passes through the

second partition wall layer **22** having a higher refractive index than the first partition wall layer **21** and the insulating film **11** and reaches the back surface (light receiving surface) **111a** of the semiconductor substrate **111**. The light **L11** that has reached the light receiving surface **111a** is photoelectrically converted by the photodiode PD. In addition, a part of the light **L11** is reflected by the surface of the insulating film **11** and the light receiving surface **111a** before reaching the photodiode PD. The reflected light **L12** passes through the second partition wall layer **22** and reaches the first partition wall layer **21**. As described above, the refractive index n_{22} of the second partition wall layer **22** is larger than the refractive index n_{21} of the first partition wall layer **21** ($n_{21} < n_{22}$). For this reason, at least a part of the light **L12** that has reached the first partition wall layer **21** is reflected again toward the second partition wall layer **22** side. The reflected light **L13** passes through the second partition wall layer **22** and the insulating film **11**, reaches the back surface (light receiving surface) **111a** of the semiconductor substrate **111**, and is photoelectrically converted by the photodiode PD.

[0124] In the imaging device **100B**, the high-angle incident light that has reached the side surface of the first metal layer **20** is also attenuated while being repeatedly reflected between the side surface of the first metal layer **20** and the first partition wall layer **21**. Accordingly, the imaging device **100B** can reduce the high-angle incident light that reaches the photodiode PD. The imaging device **100B** can inhibit deterioration in imaging performance due to the problem that the high-angle incident light is photoelectrically converted and causes color mixing or the like in a pixel signal.

[0125] Further, the first partition wall layer **21** and the second partition wall layer **22** also function as antireflection films that prevent light from being reflected from the photodiode PD side to the color filter CF side. The first partition wall layer **21** and the second partition wall layer **22** reflect the light reflected by the light receiving surface **111a** of the semiconductor substrate **111** toward the light receiving surface **111a** again. Thus, the imaging device **100B** can increase the quantum efficiency.

[0126] Next, a method for manufacturing the imaging device **100B** shown in FIG. **8** will be described. FIGS. **10A**, **10B**, **10C**, **10D**, and **10E** are cross-sectional views showing the method for manufacturing the imaging device **100B** according to the third embodiment of the present disclosure in the order of processes. In FIG. **10A**, processes up to the process of forming the first metal layer **20** are the same as those in the method for manufacturing the imaging device **100** described in the first embodiment.

[0127] After the first metal layer **20** has been formed, as shown in FIG. **10B**, the manufacturing device forms the second partition wall layer **22** above the semiconductor substrate **111**. For example, the second partition wall layer **22** is a silicon carbide film (a-SiC) having an amorphous crystal structure, and a forming method thereof is a CVD method. The manufacturing device forms the second partition wall layer **22** to be thinner than the insulating layer **22'** (see FIG. **4E**).

[0128] Next, as shown in FIG. **10C**, the manufacturing device forms the first partition wall layer **21** on the second partition wall layer **22**. For example, the first partition wall layer **21** is a silicon oxide film (SiO₂), and a forming method thereof is a CVD method. The manufacturing device forms the first partition wall layer **21** to be thinner than the insulating layer **21'** (see FIG. **4H**). Thus, the partition wall **2** having the first metal layer **20**, the first partition wall layer **21**, and the second partition wall layer **22** is finally formed. Further, a laminated structure having the second partition wall layer **22** and the first partition wall layer **21** is finally formed above the photodiodes PDs.

[0129] The subsequent processes are the same as those in the method for manufacturing the imaging device **100** described in the first embodiment. As shown in FIG. **10D**, the manufacturing device forms the color filters CFs in regions between adjacent partition walls **20** (that is, above the photodiodes PDs). Next, as shown in FIG. **10E**, the manufacturing device forms the micro lens ML above each of the plurality of color filters CFs. Through the above processes, the imaging device **100B** shown in FIG. **8** is finally formed.

Fourth Embodiment

[0130] In the first embodiment, an aspect in which only the insulating film **11** is disposed between the semiconductor substrate **111** and the partition wall **2** has been shown. However, in the embodiments of the present disclosure, a structure between the semiconductor substrate **111** and the partition wall **2** is not limited thereto. A light-shielding film may be disposed between the semiconductor substrate **111** and the partition wall **2**. Also, this light-shielding film may be made of a metal.

[0131] FIG. **11** is a cross-sectional view showing a configuration example of a partition wall **2** and a peripheral portion thereof in an imaging device **100C** according to a fourth embodiment of the present disclosure. As shown in FIG. **8**, in the imaging device **100C**, a metal light-shielding film **30** (an example of the “light-shielding film” of the present disclosure) and an insulating film **31** that covers an upper surface and side surfaces of the metal light-shielding film **30** are provided between the semiconductor substrate **111** and the partition wall **2**. For example, the insulating film **11**, the metal light-shielding film **30**, and the insulating film **31** are laminated in order from the semiconductor substrate **111** side to the partition wall **2** side. The metal light-shielding film **30** prevents light trapped in the second partition wall layer **22** of the partition wall **2** from being incident on the semiconductor substrate **111**. The metal light-shielding film **30** has a shape that exposes an upper side of the photodiode PD and covers other regions.

[0132] For example, a width **W30** of the metal light-shielding film **30** is larger than a width **W20** of the first metal layer **20** of the partition wall **2** ($W30 > W20$). Further, the width **W30** of the metal light-shielding film **30** preferably has a size equal to or larger than a value obtained by adding the width **W20** of the first metal layer **20** of the partition wall **2**, a thickness **W22** of a portion of the second partition wall layer **22** that covers the first side surface **20a** of the first metal layer **20**, and a thickness **W22** of a portion of the second partition wall layer **22** that covers the second side surface **20b** of the first metal layer **20** ($W30 \geq W20 + W22 \times 2$). Thus, the metal light-shielding film **30** can be interposed between the second partition wall layer **22** and the semiconductor substrate **111** and can prevent light from being incident the semiconductor substrate **111** from the second partition wall layer **22**.

[0133] FIG. **12** is a cross-sectional view for explaining light shielding from the partition wall **2** side to the semiconductor substrate **111** side in the imaging device **100C** according to the fourth embodiment of the present disclosure. Also, FIG. **12** shows an aspect in which the insulating film **31** shown in FIG. **11** is omitted. As shown in FIG. **12**, light **L21** that is incident on the surface of the color filter CF at a high angle, passes through the first partition wall layer **21**, and is incident on the second partition wall layer **22** proceeds to the semiconductor substrate **111** side (downward in FIG. **12**) while being reflected between the first metal layer **20** and the first partition wall layer **21**. When the light **L21** reaches a surface of the metal light-shielding film **30**, it is reflected by the surface of the first metal layer **20** and proceeds to a side opposite to the semiconductor substrate **111** (upward in FIG. **12**).

[0134] Thus, the metal light-shielding film **30** can prevent the light **L21** from being incident on the semiconductor substrate **111** from the second partition wall layer **22**. The imaging device **100C** can further reduce the high-angle incident light that reaches the photodiode PD. The imaging device **100C** can further inhibit deterioration in imaging performance due to the problem that the high-angle incident light is photoelectrically converted and causes color mixing or the like in a pixel signal.

[0135] Next, a method for manufacturing the imaging device **100C** shown in FIG. **12** will be described. FIGS. **13A**, **13B**, **13C**, **13D**, **13E**, **13F**, **13G**, and **13H** are cross-sectional views showing the method for manufacturing the imaging device **100C** according to the fourth embodiment of the present disclosure in the order of processes.

[0136] In FIG. **13A**, processes up to the process of forming the insulating film **11** are the same as those in the method for manufacturing the imaging device **100** described in the first embodiment.

After the insulating film **11** has been formed, the manufacturing device forms a metal film **30'** on the insulating film **11**. For example, the metal film **30'** is copper (Cu) or tungsten (W), and a forming method thereof is a CVD method, a vapor deposition method, or a sputtering method. [0137] Next, as shown in FIG. **13B**, the manufacturing device forms a resist pattern **RP3** on the metal film **30'**. The resist pattern **RP3** has a shape that exposes an upper side of the photodiode **PD** and covers other regions. The resist pattern **RP3** has a shape that covers a region serving as the metal light-shielding film **30** (see FIG. **12**) and exposes other regions. Next, the manufacturing device dry-etches the metal film **30'** using the resist pattern **RP3** as a mask. Dry etching is, for example, RIE. Thus, as shown in FIG. **13C**, the metal light-shielding film **30** is formed. After that, the manufacturing device removes the resist pattern **RP3**.

[0138] Next, the manufacturing device forms an insulating film on the insulating film **11**. The insulating film is, for example, a silicon oxide film (SiO₂). Next, the manufacturing device forms a resist pattern (not shown) on the insulating film and dry-etches the insulating film using the resist pattern as a mask. Dry etching is, for example, RIE. Thus, as shown in FIG. **13D**, the insulating film **31** that covers the upper surface and the side surfaces of the metal light-shielding film **30** is formed. Further, in the present embodiment, the dry etching of the insulating film can also be omitted. In that case, the upper side of the photodiode **PD** is also covered with the insulating film **31**.

[0139] Next, the manufacturing device forms a metal layer (not shown) above the semiconductor substrate **111**. For example, the metal layer is a thin film of copper (Cu) or tungsten (W), and a forming method thereof is a CVD method, a vapor deposition method, or a sputtering method. Next, the manufacturing device forms a resist pattern (not shown) on the insulating film and dry-etches the metal film using the resist pattern as a mask. Dry etching is, for example, RIE. Thus, as shown in FIG. **13E**, the first metal layer **20** is formed on the metal light-shielding film **30** via the insulating film **31**.

[0140] The subsequent processes are the same as those in the method for manufacturing the imaging device **100B** described in the third embodiment. As shown in FIG. **13F**, the manufacturing device forms the second partition wall layer **22** above the semiconductor substrate **111**. Next, as shown in FIG. **13G**, the manufacturing device forms the first partition wall layer **21** on the second partition wall layer **22**. Thus, the partition wall **2** having the first metal layer **20**, the first partition wall layer **21**, and the second partition wall layer **22** is finally formed. Further, a laminated structure having the second partition wall layer **22** and the first partition wall layer **21** is finally formed above the photodiodes **PDs**. Next, as shown in FIG. **13H**, the manufacturing device forms the color filters **CFs** in regions between adjacent partition walls **20** (that is, above the photodiodes **PDs**). Next, the manufacturing device forms the micro lens (not shown) above each of the plurality of color filters **CFs**. Through the above processes, the imaging device **100C** shown in FIG. **12** is finally formed.

Fifth Embodiment

[0141] In the above embodiment, a case in which the thicknesses **W22** (see FIG. **11**) of the second partition wall layers **22** between the plurality of pixels **102** are the same has been shown. However, the embodiments of the present disclosure are not limited thereto. In the embodiments of the present disclosure, in the second partition wall layer **22**, the thickness of the portion that covers the first side surface **20a** of the first metal layer **20** and the thickness of the portion that covers the second side surface **20b** may be different from each other.

[0142] FIG. **14** is a cross-sectional view showing a configuration example of a partition wall **2** and a peripheral portion thereof in an imaging device **100D** according to a fifth embodiment of the present disclosure. As shown in FIG. **14**, in the imaging device **100D**, a thickness **W22B** of the second partition wall layer **22** of the blue (B) pixel **102**, a thickness **W22G** of the second partition wall layer **22** of the green (G) pixel **102**, and a thickness **W22R** of the second partition wall layer **22** of the red (R) pixel **102** are different from each other. For example, among the thicknesses

W22B, W22G, and W22R, W22B is the smallest and W22R is the largest. Similarly to wavelengths of the blue (B), green (G), and red (R) colors, the relationship of $W22B < W22G < W22R$ is established. The imaging device **100D** makes the thickness of the second partition wall layer **22** different for each of the blue (B), green (G), and red (R) colors, so that a width and a pixel area of the pixel **102** can be made different for each of the blue (B), green (G), and red (R) colors. [0143] In the imaging device **100D**, the high-angle incident light that has reached the side surface of the first metal layer **20** is also attenuated while being repeatedly reflected between the side surface of the first metal layer **20** and the first partition wall layer **21**. Accordingly, the imaging device **100D** can reduce the high-angle incident light that reaches the photodiode PD. The imaging device **100D** can inhibit deterioration in imaging performance due to the problem that the high-angle incident light is photoelectrically converted and causes color mixing or the like in a pixel signal.

[0144] Next, a method for manufacturing the imaging device **100D** shown in FIG. **14** will be described. FIGS. **15A** and **15B** are cross-sectional views showing the method for manufacturing the imaging device **100D** according to the fifth embodiment of the present disclosure in the order of processes. In FIG. **15A**, processes up to the process of forming the insulating layer **22'** are the same as those in the method for manufacturing the imaging device **100** described in the first embodiment. After the insulating layer **22'** has been formed, the manufacturing device forms resist patterns **RP5** on the insulating layer **22'** as shown in FIG. **15A**. The resist patterns **RP5** have shapes that cover regions serving as the first metal layer **20** and the second partition wall layer **22** (see FIG. **14**) of the partition wall **2** and expose other regions.

[0145] In the imaging device **100**, thicknesses of the second partition wall layers **22** between the blue (B), green (G), and red (R) pixels **102** are different from each other. For example, boundary portions between the blue (B), green (G), and red (R) pixels **102** are first metal layers **20**, and a thickness of the second partition wall layer **22** formed on the first side surface **20a** side of the first metal layer **20** and a thickness of the second partition wall layer **22** formed on the second side surface **20b** side are different from each other. For this reason, a central position **CRP5** in a width direction of the resist pattern **RP5** is deviated in the width direction from a central position **C20** in the width direction of the first metal layer **20**.

[0146] Further, the plurality of resist patterns **RP5** have different widths depending on their arrangement positions. For example, a width **WRP5** of a resist pattern **RP5** disposed at a position straddling between the blue (B) pixel **102** and the green (G) pixel **102** is larger than a width **WRP5** of a resist pattern **RP5** formed to straddle between the green (G) pixel **102** and the red (R) pixel **102**.

[0147] Next, the manufacturing device dry-etches the insulating layer **22'** using the resist patterns **RP5** as a mask. Dry etching is, for example, RIE. Thus, as shown in FIG. **15B**, the second partition wall layers **22** are formed. After that, the manufacturing device removes the resist patterns **RP5**.

[0148] The subsequent processes are the same as those in the method for manufacturing the imaging device **100** described in the first embodiment. The manufacturing device forms the first partition wall layers **21** (see FIG. **14**), forms the color filters **CFs** (see FIG. **14**), and forms the micro lenses **MLs** (see FIG. **14**). Through the above processes, the imaging device **100D** shown in FIG. **14** is finally formed.

Sixth Embodiment

[0149] In the embodiments of the present disclosure, widths of the color filters **CFs** may be the same length or different lengths from each other between the plurality of pixels **102**. FIG. **16** is a cross-sectional view showing a configuration example of a partition wall **2** and a peripheral portion thereof in an imaging device **100E** according to a sixth embodiment of the present disclosure. As shown in FIG. **16**, in the imaging device **100E**, a width **WCFCB** of the blue (B) color filter **CF**, a width **WCFCG** of the green (G) color filter **CF**, and a width **WCFCR** of the red (R) color filter **CF** are different from each other.

[0150] For example, among the widths WCFB, WCFG, and WCFR, WCFB is the largest, and WCFR is the smallest. Among the blue (B), green (G), and red (R) pixels **102**, the red (R) pixel **102** has the highest sensitivity, and the blue (B) pixel **102** has the lowest sensitivity. For this reason, in the imaging device **100D**, the width WCFE of the color filter CF is reduced to bring the sensitivity of the red (R) closer to the sensitivity of the green (G). Further, the width WCFE of the blue (B) color filter CF is increased to bring the sensitivity of the blue (B) closer to the sensitivity of the green (G). Contrary to the sensitivities of the blue (B), green (G), and red (R), the relationship of $WCFB > WCFG > WCFR$ is established.

[0151] Further, in the imaging device **100E**, similarly to the imaging device **100D** described in the fifth embodiment, the thickness W22B of the second partition wall layer **22** of the blue (B) pixel **102**, the thickness W22G of the second partition wall layer **22** of the green (G) pixel **102**, and the thickness W22R of the second partition wall layer **22** of the red (R) pixel **102** may be different from each other.

[0152] For example, the relationship of $W22B < W22G < W22R$ may be established. In the imaging device **100E**, the thickness of the second partition wall layer **22** is made different for each of the blue (B), green (G), and red (R), and thus the blue (B), green (G), and red (R) pixels **102** have the same width. Specifically, the relationship of $WCFB + W22B \times 2 = WCFG + W22G \times 2 = WCFR + W22R \times 2$ is established. Thus, the blue (B), green (G), and red (R) pixels **102** have the same width, and the micro lenses ML disposed on the color filters CFs also have the same width (diameter). In each of the blue (B), green (G), and red (R) pixels **102**, the pixel area is made uniform.

[0153] In the imaging device **100E**, the high-angle incident light that has reached the side surface of the first metal layer **20** is also attenuated while being repeatedly reflected between the side surface of the first metal layer **20** and the first partition wall layer **21**. Accordingly, the imaging device **100E** can reduce the high-angle incident light that reaches the photodiode PD. The imaging device **100E** can inhibit deterioration in imaging performance due to the problem that the high-angle incident light is photoelectrically converted and causes color mixing or the like in a pixel signal.

Seventh Embodiment

[0154] The semiconductor substrates of the imaging devices according to the embodiments of the present disclosure may be provided with trench isolation for separating the photodiodes PDs adjacent to each other. Also, the imaging devices according to the embodiments of the present disclosure may be subjected to so-called “pupil correction.”

[0155] FIG. **17** is a diagram illustrating a central region AR1 and a peripheral region AR2 of an imaging region configured of a plurality of photodiodes in an imaging device **100F** according to a seventh embodiment of the present disclosure. FIG. **18** is the imaging device **100F** according to the seventh embodiment of the present disclosure and is a cross-sectional view showing a configuration example of a partition wall **2** and a peripheral portion thereof in the peripheral region AR2 of the imaging region shown in FIG. **17**.

[0156] As shown in FIG. **18**, a trench isolation **5** (an example of the “element separation layer” of the present disclosure) that separates one photodiode PD from another photodiode PD, which are adjacent to each other, may be provided in the semiconductor substrate **111** of the imaging device **100F**. The trench isolation **5** is configured of a trench provided in the semiconductor substrate **111** and an insulating film (for example, SiO.sub.2) filled in the trench. The partition wall **2** is located on the trench isolation **5**. Also, in the embodiments of the present disclosure, the trench isolation **5** deeply formed on the semiconductor substrate **111** may be referred to as a deep trench isolation (DTI).

[0157] In addition, the imaging device **100F** is subjected to so-called “pupil correction.” For example, the partition wall **2** that separates the color filters CFs adjacent to each other is shifted toward the central region AR1 side of the imaging device by a predetermined distance Wgap with

respect to the trench isolation **5** that separates adjacent photodiodes PDs from each other. This distance (an amount of shift) W_{gap} increases toward a side further separated from the central region **AR1**. Thus, the imaging device **100F** can deviate a range of angle at which light can be incident in the peripheral region **AR2** toward an upper side of the central region **AR1**, so that light collection efficiency in the peripheral region **AR2** can be improved.

Eighth Embodiment

[0158] In the embodiments of the present disclosure, the trench isolation **5** that separates the photodiodes PDs adjacent to each other may include a metal layer (hereinafter referred to as a second metal layer). The second metal layer included in the trench isolation **5** may be joined or integrally formed with the first metal layer **20** included in the partition wall **2** to be integrated therewith, or may be separated therefrom.

[0159] FIG. **19** is a cross-sectional view showing a configuration example of a partition wall **2** and a peripheral portion thereof in an imaging device **100G** according to an eighth embodiment of the present disclosure. As shown in FIG. **19**, the semiconductor substrate **111** of the imaging device **100G** is provided with a trench isolation **5** that separates adjacent photodiodes PDs from each other. In the imaging device **100G**, the trench isolation **5** has a second metal layer **50** located in a central portion of the trench isolation **5**, a first translucent insulating layer **51** that covers the second metal layer **50** from an outer side thereof, and a second insulating layer **52** located between the second metal layer **50** and the first insulating layer **51**. The first insulating layer **51** and the second insulating layer correspond to the “insulating layer” of the present disclosure.

[0160] For example, in a thickness direction of the imaging device **100G** (that is, a normal direction of the light receiving surface **111a**), the second metal layer **50** included in the trench isolation **5** and the first metal layer **20** included in the partition wall **2** overlap each other. Similarly, the first insulating layer **51** and the first partition wall layer **21** overlap each other, and the second insulating layer **52** and the second partition wall layer **22** also overlap each other. A width W_{50} of the first metal layer **20** may be the same as or different from the width W_{20} of the first metal layer **20**. FIG. **19** shows a case in which $W_{50}=W_{20}$, but this is just an example. $W_{50}<W_{20}$ may be used, or $W_{50}>W_{20}$ may be used.

[0161] Materials constituting the second metal layer **50**, the first insulating layer **51**, and the second insulating layer **52** are not particularly limited, but as an example, the second metal layer **50** is made of copper (Cu) or tungsten (W), the first insulating layer **51** is made of a silicon oxide film (SiO_2), and the second insulating layer **52** is made of a silicon carbide film (a-SiC) having an amorphous crystal structure.

[0162] In a case in which the first metal layer **20** and the second metal layer **50** are made of the same material, the first metal layer **20** and the second metal layer **50** are easily joined to each other. Further, in a case in which the first metal layer **20** and the second metal layer **50** are made of the same material, the first metal layer **20** and the second metal layer **50** may be integrally formed. By joining or integrally forming the first metal layer **20** and the second metal layer **50** and integrating them, it is possible to improve a joining strength of the partition wall **2** for the semiconductor substrate **111**.

[0163] In a case in which the first insulating layer **51** and the first partition wall layer **21** are made of the same material, the first insulating layer **51** and the first partition wall layer **21** are easily joined to each other, and thus it is possible to improve the joining strength of the partition wall **2** for the semiconductor substrate **111**. Similarly, in a case in which the second insulating layer **52** and the second partition wall layer **22** are made of the same material, the second insulating layer **52** and the second partition wall layer **22** are easily joined to each other, and thus it is possible to improve the joining strength of the partition wall **2** for the semiconductor substrate **111**.

[0164] Next, a method for manufacturing the imaging device **100G** shown in FIG. **19** will be described. FIGS. **20A**, **20B**, **20C**, **20D**, **20E**, **20F**, and **20G** are cross-sectional views showing the method for manufacturing the imaging device **100G** according to the eighth embodiment of the

present disclosure in the order of processes. As shown in FIG. 20A, the manufacturing device forms the insulating film **11** on the light receiving surface **111a** of the semiconductor substrate **111** on which the photodiode PD is formed. Next, the manufacturing device etches the insulating film **11** and the semiconductor substrate **111** to form a trench H1. The trench H1 is formed between one photodiode PD1 and another photodiode PD which are adjacent to each other. Next, as shown in FIG. 20B, the manufacturing device forms an insulating layer **51'** on the light receiving surface **111a** side of the semiconductor substrate **111** to fill the trench H1. For example, the insulating layer **51'** is a silicon oxide film (SiO₂), and a forming method thereof is a CVD method. Next, the manufacturing device performs a CMP treatment to a surface of the insulating layer **51'** to flatten the surface of the insulating layer **51'**.

[0165] Next, as shown in FIG. 20C, the manufacturing device forms a resist pattern RP6 on the insulating layer **51'**. The resist pattern RP6 has a shape that opens a region in which the second metal layer **50** (see FIG. 19) is formed and a region in which the second insulating layer **52** (see FIG. 19) is formed in the trench isolation **5** and covers other regions. Next, the manufacturing device dry-etches the insulating layer **51'** using the resist pattern RP6 as a mask. Thus, as shown in FIG. 20C, the first insulating layer **51** disposed in the trench H1 is formed. After the first insulating layer **51** has been formed, the manufacturing device removes the resist pattern RP6.

[0166] Next, as shown in FIG. 20D, the manufacturing device forms an insulating layer **52'** above the light receiving surface **111a**. For example, the insulating layer **52'** is a silicon carbide film (a-SiC) having an amorphous crystal structure, and a forming method thereof is a CVD method. Next, the manufacturing device partially dry-etches the insulating layer **52'** and removes the insulating layer **52'** from regions other than the trench H1. The insulating layer **52'** remaining in the trench H1 becomes the second insulating layer **52**. Also, in the present embodiment, dry etching of the insulating layer **52'** may be omitted. In this case, the entire semiconductor substrate **111** on the light receiving surface **111a** side has a structure in which it is covered with the insulating layer **52'** (that is, the second insulating layer **52**).

[0167] Next, as shown in FIG. 20E, the manufacturing device forms a metal layer **50'** on the light receiving surface **111a** side. For example, the metal layer **50'** is a thin film of copper (Cu) or tungsten (W), and a forming method thereof is a vapor deposition or sputtering method. The trench H1 has a structure in which it is filled with the first insulating layer **51**, the second insulating layer **52**, and the metal layer **50'**.

[0168] Next, as shown in FIG. 20F, the manufacturing device forms a resist pattern RP7 on the metal layer **50'**. The resist pattern RP7 has a shape that covers a region serving as the first metal layer **20** (see FIG. 2) and exposes other regions. Next, the manufacturing device dry-etches the metal layer **50'** using the resist pattern RP7 as a mask. Thus, as shown in FIG. 20G, the first metal layer **20** and the second metal layer **50** are formed from the metal layer **50'**. By forming the second metal layer **50**, the trench isolation **5** is finally formed. After that, the manufacturing device removes the resist pattern RP7.

[0169] The subsequent processes are, for example, the same as those in the method for manufacturing the imaging device **100** described in the first embodiment. Through the processes shown in FIGS. 4E, 4F, 4G, 4H, 4I, 4J, and 4K, the imaging device **100G** shown in FIG. 19 is finally formed.

Ninth Embodiment

[0170] In the embodiments of the present disclosure, a light-shielding film may be disposed between the second metal layer **50** of the trench isolation **5** and the first metal layer **20** of the partition wall **2**. Also, this light-shielding film may be made of a metal.

[0171] FIG. 21 is a cross-sectional view showing a configuration example of a partition wall **2** and a peripheral portion thereof in an imaging device **100H** according to a ninth embodiment of the present disclosure. As shown in FIG. 21, in the imaging device **100H**, the metal light-shielding film **30** and the insulating film **31** that cover the upper surface and side surfaces of the metal light-

shielding film **30** are provided between the second metal layer **50** of the trench isolation **5** and the first metal layer **20** of the partition wall **2**. The metal light-shielding film **30** and the insulating film **31** are laminated in order from the trench isolation **5** side to the partition wall **2** side. The metal light-shielding film **30** prevents light trapped in the second partition wall layer **22** of the partition wall **2** from entering the trench isolation **5**.

[0172] For example, the width W_{30} of the metal light-shielding film **30** is larger than the width W_{50} of the second metal layer **50** ($W_{30} > W_{50}$). Further, the width W_{30} of the metal light-shielding film **30** preferably has a size equal to or larger than a value obtained by adding the width W_{50} of the second metal layer **50**, a thickness W_{52} of a portion of the second insulating layer **52** that covers one side surface of the second metal layer **50**, and a thickness W_{52} of a portion of the second insulating layer **52** that covers another side surface of the second metal layer **50** ($W_{30} \geq W_{50} + W_{52} \times 2$). Thus, the metal light-shielding film **30** can cover the second metal layer **50** and the second insulating layer **52**. The metal light-shielding film **30** can prevent light from entering the second metal layer **50** and the second insulating layer **52** from the second partition wall layer **22**.

[0173] Next, a method for manufacturing the imaging device **100H** shown in FIG. **21** will be described. FIGS. **22A**, **22B**, **22C**, **22D**, **22E**, **22F**, **22G**, **22H**, **22I**, **22J**, **22K**, and **22L** are cross-sectional views showing the method for manufacturing the imaging device **100H** according to the ninth embodiment of the present disclosure in the order of processes. In FIG. **22A**, processes up to the process of forming the trench **H1** are the same as those in the method for manufacturing the imaging device **100G** described in the eighth embodiment. After the trench **H1** has been formed, as shown in FIG. **22B**, the manufacturing device forms the insulating layer **51'** on the insulating film **11**. For example, the insulating layer **51'** is a silicon oxide film (SiO_2), and a forming method thereof is a CVD method.

[0174] Next, as shown in FIG. **22C**, the manufacturing device forms the insulating layer **52'** on the insulating layer **51'** to fill the trench **H1**. For example, the insulating layer **52'** is a silicon carbide film (a-SiC) having an amorphous crystal structure, and a forming method thereof is a CVD method. Next, as shown in FIG. **22D**, the manufacturing device performs a CMP treatment to the surface of the insulating layer **52'** to remove the insulating layer **52'** from the regions other than the trench **H1**. Further, the manufacturing device also performs a CMP treatment to the surface of the insulating layer **51'** exposed from below the insulating layer **52'** to remove the insulating layer **51'** from the regions other than the trench **H1**. Thus, the first insulating layer **51** disposed in the trench **H1** is formed. Also, in the present embodiment, the CMP treatment for the insulating layer **51'** may be omitted. In this case, the entire semiconductor substrate **111** on the light receiving surface **111a** side has a structure in which it is covered with the insulating layer **51'** (that is, the first insulating layer **51**).

[0175] Next, as shown in FIG. **22E**, the manufacturing device forms a resist pattern **RP8** on the light receiving surface **111a** side of the semiconductor substrate **111**. The resist pattern **RP8** has a shape that opens a region of the trench isolation **5** in which the second metal layer **50** (see FIG. **21**) is formed and covers other regions. Next, the manufacturing device dry-etches the insulating layer **52'** using the resist pattern **RP8** as a mask. Thus, the second insulating layer **52** disposed in the trench **H1** is formed. After the second insulating layer **52** has been formed, the manufacturing device removes the resist pattern **RP8**.

[0176] Next, as shown in FIG. **22F**, the manufacturing device forms the metal layer **50'** on the light receiving surface **111a** side. For example, the metal layer **50'** is a thin film of copper (Cu) or tungsten (W), and a forming method thereof is a vapor deposition or sputtering method. The trench **H1** has a structure in which it is filled with the first insulating layer **51**, the second insulating layer **52**, and the metal layer **50'**.

[0177] Next, as shown in FIG. **20G**, the manufacturing device forms a resist pattern **RP9** on the metal layer **50'**. The resist pattern **RP9** has a shape that covers the region serving as the metal light-

shielding film **30** (see FIG. **21**) and exposes other regions. Next, the manufacturing device dry-etches the metal layer **50'** using the resist pattern **RP8** as a mask. Thus, the second metal layer **50** of the trench isolation **5** and the metal light-shielding film **30** are formed from the metal layer **50'**. By forming the second metal layer **50**, the trench isolation **5** is finally formed. After that, the manufacturing device removes the resist pattern **RP9**.

[0178] Next, as shown in FIG. **22H**, the manufacturing device forms the insulating film **31** on the light receiving surface **111a** side of the semiconductor substrate **111** to cover the metal light-shielding film **30**. The method for forming the insulating film **31** is, for example, a CVD method. Next, as shown in FIG. **22I**, the manufacturing device forms the metal layer **20'** on the light receiving surface **111a** side. The method for forming the metal layer **20'** is, for example, a vapor deposition or sputtering method. Next, as shown in FIG. **22J**, the manufacturing device forms a resist pattern **RP10** on the metal layer **20'**. The resist pattern **RP10** has a shape that covers the region serving as the first metal layer **20** (see FIG. **21**) and exposes other regions. Next, the manufacturing device dry-etches the metal layer **20'** using the resist pattern **RP10** as a mask. Thus, the first metal layer **20** is formed from the metal layer **20'**. After that, the manufacturing device removes the resist pattern **RP10**.

[0179] Next, as shown in FIG. **22K**, the manufacturing device forms the insulating layer **22'** above the light receiving surface **111a**. For example, the insulating layer **22'** is a silicon carbide film (a-SiC) having an amorphous crystal structure, and a forming method thereof is a CVD method. Next, as shown in FIG. **22L**, the manufacturing device forms a resist pattern **RP11** on the insulating layer **22'**. The resist pattern **RP11** has a shape that covers the regions serving as the first metal layer **20** and the second partition wall layer **22** (see FIG. **21**) and exposes other regions. Next, the manufacturing device dry-etches the insulating layer **22'** using the resist pattern **RP10** as a mask. Thus, the second partition wall layer **22** is formed from the insulating layer **22'**. After that, the manufacturing device removes the resist pattern **RP10**.

[0180] The subsequent processes are, for example, the same as those in the method for manufacturing the imaging device **100** described in the first embodiment. Through the processes shown in FIGS. **4H**, **4I**, **4J**, and **4K**, the imaging device **100H** shown in FIG. **21** is finally formed.

OTHER EMBODIMENTS

[0181] While the present disclosure has been described on the basis of the embodiments and modified examples as described above, the descriptions and figures that constitute parts of the disclosure are not intended to be understood as limiting the present disclosure. Various alternative embodiments, examples, and operable techniques will be apparent to those skilled in the art from this disclosure. It goes without saying that the technique according to the present disclosure (the present technique) includes various embodiments and the like that have not been described herein. At least one of various omissions, substitutions, and modifications of constituent elements may be performed without departing from the gist of the embodiments described above. Further, the effects described in the present specification are merely exemplary and not intended as limiting, and other effects may be provided.

<Example of Application to Electronic Device>

[0182] For example, the technique according to the present disclosure (the present technique) can be applied to various electronic devices such as an imaging system such as a digital still camera, a digital video camera, or the like (hereinafter collectively referred to as a camera), a mobile device such as a mobile phone having an imaging function, or other devices having an imaging function.

[0183] FIG. **23** is a conceptual diagram showing an example in which the technique according to the present disclosure (the present technique) is applied to an electronic device **300**. As shown in FIG. **23**, the electronic device **300** is, for example, a camera and has a solid-state imaging device **201**, an optical lens **210**, a shutter device **211**, a drive circuit **212**, and a signal processing circuit **213**. The optical lens **210** is an example of the "optical component" of the present disclosure.

[0184] Light transmitted through the optical lens **210** is incident on the solid-state imaging device

201. For example, the optical lens **210** forms an image of image light (incident light) from a subject on an imaging surface of the solid-state imaging device **201**. Thus, signal charges are accumulated in the solid-state imaging device **201** for a certain period of time. The shutter device **211** controls a light irradiation period and a light blocking period for the solid-state imaging device **201**. The drive circuit **212** supplies a drive signal for controlling a transfer operation or the like of the solid-state imaging device **201** and a shutter operation of the shutter device **211**. Signal transfer of the solid-state imaging device **201** is performed by the drive signal (timing signal) supplied from the drive circuit **212**. The signal processing circuit **213** performs various signal processing. For example, the signal processing circuit **213** processes a signal output from the solid-state imaging device **201**. A video signal that has undergone signal processing is stored in a storage medium such as a memory, or is output to a monitor.

[0185] Also, the shutter operation in the electronic device **300** may be realized by an electronic shutter (for example, a global shutter) operated by the solid-state imaging device **201** instead of a mechanical shutter. In a case in which the shutter operation in the electronic device **300** is realized by the electronic shutter, the shutter device **211** in FIG. **23** may be omitted.

[0186] In the electronic device **300**, any one or more of the above-described imaging devices **100**, **100A**, **100B**, **100C**, **100D**, **100E**, **100F**, **100G**, and **100H** is applied to the solid-state imaging device **201**. Thus, it is possible to obtain the electronic device **300** with improved performance. Also, the electronic device **300** is not limited to the camera. The electronic device **300** may be a mobile device such as a mobile phone having an imaging function, or other devices having an imaging function.

<Example of Application to Endoscopic Operation System>

[0187] The technique according to the present disclosure (the present technique) can be applied to various products. For example, the technique according to the present disclosure may be applied to an endoscopic operation system.

[0188] FIG. **24** is a diagram showing an example of a schematic configuration of an endoscopic operation system to which the technique according to the present disclosure (the present technique) may be applied.

[0189] FIG. **24** shows a situation in which an operator (doctor) **11131** is performing an operation on a patient **11132** on a patient bed **11133** using the endoscopic operation system **11000**. As illustrated, the endoscopic operation system **11000** is configured of an endoscope **11100**, other surgical instruments **11110** such as a pneumoperitoneum tube **11111** and an energized treatment tool **11112**, a support arm device **11120** that supports the endoscope **11100**, and a cart **11200** equipped with various devices for endoscopic operations.

[0190] The endoscope **11100** is configured of a lens barrel **11101**, a region of which having a predetermined length from a tip is inserted into a body cavity of the patient **11132**, and a camera head **11102** connected to a base end of the lens barrel **11101**. Although the endoscope **11100** configured as a so-called rigid mirror having the rigid lens barrel **11101** is illustrated in the illustrated example, the endoscope **11100** may be configured as a so-called flexible mirror having a flexible lens barrel.

[0191] An opening portion into which an objective lens is fitted is provided at the tip of the lens barrel **11101**. A light source device **11203** is connected to the endoscope **11100**, and light generated by the light source device **11203** is guided to the tip of the lens barrel by a light guide provided to extend inside the lens barrel **11101** and is radiated toward an observation target in the body cavity of the patient **11132** via the objective lens. Also, the endoscope **11100** may be a forward-viewing endoscope, a perspective-viewing endoscope, or a side-viewing endoscope.

[0192] An optical system and an imaging element are provided inside the camera head **11102**, and the reflected light (observation light) from the observation target is condensed on the imaging element by the optical system. The observation light is photoelectrically converted by the imaging element, and an electrical signal corresponding to the observation light, that is, an image signal

corresponding to an observed image is generated. The image signal is transmitted as RAW data to a camera control unit (CCU) **11201**.

[0193] The CCU **11201** is configured of a central processing unit (CPU), a graphics processing unit (GPU) or the like, and comprehensively controls operations of the endoscope **11100** and a display device **11202**. Further, the CCU **11201** receives the image signal from the camera head **11102** and performs various types of image processing for displaying an image based on the image signal, for example, development processing (demosaic processing) and the like, on the image signal.

[0194] The display device **11202** displays the image based on the image signal that has been subjected to image processing by the CCU **11201** under the control of the CCU **11201**.

[0195] The light source device **11203** is configured of, for example, a light source such as a light emitting diode (LED) and supplies irradiation light, which is used when a surgical part or the like is imaged, to the endoscope **11100**.

[0196] An input device **11204** is an input interface for the endoscopic operation system **11000**. A user can input various types of information or instructions to the endoscopic operation system **11000** via the input device **11204**. For example, the user inputs an instruction to change imaging conditions (a type of irradiation light, a magnification, a focal length, or the like) of the endoscope **11100**, or the like.

[0197] A treatment tool control device **11205** controls driving of the energized treatment tool **11112** for cauterizing or incising tissue, sealing a blood vessel, or the like. A pneumoperitoneum device **11206** sends a gas into the body cavity through a pneumoperitoneum tube **11111** in order to inflate the body cavity of the patient **11132** for the purpose of securing a visual field for the endoscope **11100** and a working space for the operator. A recorder **11207** is a device capable of recording various information regarding the operation. A printer **11208** is a device that can print various types of information regarding the operation in various formats such as text, images, or graphs.

[0198] In addition, the light source device **11203** that supplies the endoscope **11100** with the irradiation light used when the surgical part is imaged can be configured of, for example, an LED, a laser light source, or a white light source configured of a combination thereof. In a case in which a white light source is configured by a combination of RGB laser light sources, it is possible to control an output intensity and an output timing of each color (each wavelength) with high accuracy, and thus white balance of captured images can be adjusted in the light source device **11203**. Further, in this case, laser light from each of the respective RGB laser light sources is radiated to the observation target in a time-division manner, and driving of the imaging element of the camera head **11102** is controlled in synchronization with a radiation timing, so that it is also possible to capture images corresponding to each of RGB in a time-division manner. According to this method, it is possible to obtain a color image without providing a color filter to the imaging element.

[0199] Further, the driving of the light source device **11203** may be controlled to change intensity of the output light at predetermined time intervals. By controlling the driving of the imaging element of the camera head **11102** in synchronization with a timing of changing the intensity of the light to acquire images in a time-division manner and combine the images, it is possible to generate a high dynamic range image without so-called blackout and whiteout.

[0200] Further, the light source device **11203** may be configured to be able to supply light having a predetermined wavelength band corresponding to special light observation. In the special light observation, for example, by emitting light in a narrower band than irradiation light (that is, white light) during normal observation using wavelength dependence of light absorption in a body tissue, so-called narrow band light observation (narrow band imaging) in which a predetermined tissue such as a blood vessel in the mucous membrane surface layer is imaged with a high contrast is performed. Alternatively, in the special light observation, fluorescence observation in which an image is obtained by fluorescence generated by emitting excitation light may be performed. The fluorescence observation can be performed by emitting excitation light to a body tissue and

observing fluorescence from the body tissue (autofluorescence observation), or locally injecting a reagent such as indocyanine green (ICG) to a body tissue and emitting excitation light corresponding to a fluorescence wavelength of the reagent to the body tissue to obtain a fluorescence image. The light source device **11203** may be configured to be able to supply narrow band light and/or excitation light corresponding to such special light observation.

[0201] FIG. **25** is a block diagram illustrating an example of a functional configuration of the camera head **11102** and CCU **11201** shown in FIG. **24**.

[0202] The camera head **11102** has a lens unit **11401**, an imaging unit **11402**, a driving unit **11403**, a communication unit **11404**, and a camera head control unit **11405**. The CCU **11201** has a communication unit **11411**, an image processing unit **11412**, and a control unit **11413**. The camera head **11102** and the CCU **11201** are connected to each other via a transmission cable **11400** so that they can communicate with each other.

[0203] The lens unit **11401** is an optical system provided at a portion for connection to the lens barrel **11101**. The observation light taken in from the tip of the lens barrel **11101** is guided to the camera head **11102** and incident on the lens unit **11401**. The lens unit **11401** is configured of a combination of a plurality of lenses including a zoom lens and a focus lens.

[0204] The imaging unit **11402** is configured of an imaging element. The imaging element constituting the imaging unit **11402** may be one element (so-called single plate type) or a plurality of elements (so-called multi-plate type). In a case in which the imaging unit **11402** is configured of a multi-plate type, for example, image signals corresponding to RGBs may be generated by imaging elements and combined with each other, so that a color image may be obtained.

Alternatively, the imaging unit **11402** may be configured to have a pair of imaging elements for acquiring image signals for the right eye and the left eye corresponding to three-dimensional (3D) display. By performing the 3D display, the operator **11131** will be able to determine a depth of biological tissue in the surgical part more accurately. In addition, in a case in which the imaging unit **11402** is configured as a multi-plate type, a plurality of lens units **11401** may be provided to correspond to the imaging elements.

[0205] Further, the imaging unit **11402** may not necessarily be provided in the camera head **11102**. For example, the imaging unit **11402** may be provided immediately after the objective lens inside the lens barrel **11101**.

[0206] The driving unit **11403** is configured of an actuator and moves the zoom lens and the focus lens of the lens unit **11401** by a predetermined distance along an optical axis under the control of the camera head control unit **11405**. Thus, the magnification and focus of the image captured by the imaging unit **11402** can be adjusted appropriately.

[0207] The communication unit **11404** is configured of a communication device for transmitting or receiving various information to or from the CCU **11201**. The communication unit **11404** transmits an image signal obtained from the imaging unit **11402** to the CCU **11201** through the transmission cable **11400** as RAW data.

[0208] Further, the communication unit **11404** receives a control signal for controlling the driving of the camera head **11102** from the CCU **11201** and supplies the control signal to the camera head control unit **11405**. The control signal includes, for example, information on imaging conditions such as information for designating a frame rate of a captured image, information for designating an exposure value at the time of imaging, and/or information for designating a magnification and a focus of the captured image.

[0209] Also, the imaging conditions such as the frame rate, the exposure value, the magnification, and the focus described above may be appropriately designated by the user or may be automatically set by the control unit **11413** of the CCU **11201** on the basis of the acquired image signal. In the latter case, a so-called auto exposure (AE) function, auto focus (AF) function and auto white balance (AWB) function are provided in the endoscope **11100**.

[0210] The camera head control unit **11405** controls the driving of the camera head **11102** on the

basis of the control signal from the CCU **11201** received via the communication unit **11404**.

[0211] The communication unit **11411** is configured of a communication device for transmitting and receiving various types of information to and from the camera head **11102**. The communication unit **11411** receives an image signal transmitted from the camera head **11102** via the transmission cable **11400**.

[0212] In addition, the communication unit **11411** transmits a control signal for controlling the driving of the camera head **11102** to the camera head **11102**. The image signal or the control signal can be transmitted through electric communication, optical communication, or the like.

[0213] The image processing unit **11412** performs various kinds of image processing on the image signal that is the RAW data transmitted from the camera head **11102**.

[0214] The control unit **11413** performs various kinds of control regarding imaging of the surgical part or the like using the endoscope **11100** and display of a captured image obtained by imaging the surgical part or the like. For example, the control unit **11413** generates the control signal for controlling the driving of the camera head **11102**.

[0215] Further, the control unit **11413** causes the display device **11202** to display the captured image obtained by imaging the surgical part or the like on the basis of the image signal that has been subjected to the image processing by the image processing unit **11412**. In this case, the control unit **11413** may recognize various objects in the captured image using various image recognition techniques. For example, the control unit **11413** can recognize surgical tools such as forceps, specific biological parts, bleeding, mist when the energized treatment tool **11112** is used, and the like by detecting an edge shape, a color, and the like of an object included in the captured image. When the control unit **11413** causes the display device **11202** to display the captured image, it may cause various types of surgical support information to be superimposed and displayed with the image of the surgical part using the recognition result. The surgical support information is superimposed and displayed, and presented to the operator **11131**, so that a burden on the operator **11131** can be reduced and the operator **11131** can surely proceed with the operation.

[0216] The transmission cable **11400** that connects the camera head **11102** to the CCU **11201** is an electrical signal cable compatible with communication of an electrical signal, an optical fiber compatible with optical communication, or a composite cable thereof.

[0217] Here, in the illustrated example, wired communication is performed using the transmission cable **11400**, but the communication between the camera head **11102** and the CCU **11201** may be performed wirelessly.

[0218] An example of the endoscopic operation system to which the technique according to the present disclosure can be applied has been described above. The technique according to the present disclosure may be applied to, for example, the endoscope **11100**, the imaging unit **11402** of the camera head **11102**, the image processing unit **11412** of the CCU **11201**, and the like among the configurations described above. Specifically, any one or more of the above-mentioned imaging devices **100**, **100A**, **100B**, **100C**, **100D**, **100E**, **100F**, **100G**, and **100H** can be applied to the imaging unit **10402**. By applying the technique according to the present disclosure to the endoscope **11100**, the imaging unit **11402** of the camera head **11102**, the image processing unit **11412** of the CCU **11201**, and the like, a clearer image of the surgical part can be obtained, and thus the operator can surely confirm the surgical part. Further, by applying the technique according to the present disclosure to the endoscope **11100**, the imaging unit **11402** of the camera head **11102**, the image processing unit **11412** of the CCU **11201**, and the like, an image of the surgical part can be obtained with lower latency, and thus it is possible to perform a treatment with the same feeling as when the operator is observing the surgical part by touch.

[0219] Also, the endoscopic operation system has been described as an example, but in addition thereto, the technique according to the present disclosure may be applied to, for example, a microscopic operation system.

<Example of Application to Mobile Object>

[0220] The technique according to the present disclosure (the present technique) can be applied in various products. For example, the technique according to the present disclosure may be realized as a device mounted in any type of mobile objects such as automobiles, electric vehicles, hybrid electric vehicles, motorbikes, bicycles, personal mobility, airplanes, drones, ships, and robots. [0221] FIG. 26 is a block diagram showing a schematic configuration example of a vehicle control system that is an example of a mobile object control system to which the technique according to the present disclosure may be applied.

[0222] A vehicle control system **12000** includes a plurality of electronic control units connected to each other via a communication network **12001**. In the example shown in FIG. 26, the vehicle control system **12000** includes a drive system control unit **12010**, a body system control unit **12020**, a vehicle external information detection unit **12030**, a vehicle internal information detection unit **12040**, and an integrated control unit **12050**. In addition, as functional configurations of the integrated control unit **12050**, a microcomputer **12051**, a sound image output unit **12052**, and an in-vehicle network interface (I/F) **12053** are shown.

[0223] The drive system control unit **12010** controls operations of devices related to the drive system of the vehicle in accordance with various programs. For example, the drive system control unit **12010** functions as a driving force generation device for generating a driving force of a vehicle such as an internal combustion engine or a driving motor, a driving force transmission mechanism for transmitting a driving force to wheels, a steering mechanism for adjusting a steering angle of a vehicle, and a control device such as a braking device that generates a braking force of a vehicle.

[0224] The body system control unit **12020** controls operations of various devices equipped in a vehicle body in accordance with various programs. For example, the body system control unit **12020** functions as a control device of a keyless entry system, a smart key system, a power window device, or various lamps such as a head lamp, a back lamp, a brake lamp, and a turn signal or fog lamp. In this case, radio waves transmitted from a portable device that substitutes for a key or signals of various switches may be input to the body system control unit **12020**. The body system control unit **12020** receives inputs of these radio waves or signals and controls a door lock device, a power window device, a lamp, and the like of a vehicle.

[0225] The vehicle external information detection unit **12030** detects information outside the vehicle in which the vehicle control system **12000** is mounted. For example, an imaging unit **12031** is connected to the vehicle external information detection unit **12030**. The vehicle external information detection unit **12030** causes the imaging unit **12031** to capture an image outside the vehicle and receives the captured image. The vehicle external information detection unit **12030** may perform object detection processing or distance detection processing for people, cars, obstacles, signs, and letters on a road on the basis of the received image.

[0226] The imaging unit **12031** is an optical sensor that receives light and outputs an electrical signal corresponding to an amount of the received light. The imaging unit **12031** can output the electrical signal as an image or as ranging information. In addition, the light received by the imaging unit **12031** may be visible light or invisible light such as infrared rays.

[0227] The vehicle internal information detection unit **12040** detects information inside the vehicle. For example, a driver state detection unit **12041** that detects a state of a driver is connected to the vehicle internal information detection unit **12040**. The driver state detection unit **12041** includes, for example, a camera that captures an image of the driver, and the vehicle internal information detection unit **12040** may calculate a degree of fatigue or concentration of the driver or may determine whether or not the driver is dozing on the basis of detection information input from the driver state detection unit **12041**.

[0228] The microcomputer **12051** can calculate a control target value of the driving force generation device, the steering mechanism, or the braking device on the basis of information inside and outside the vehicle acquired by the vehicle external information detection unit **12030** or the vehicle internal information detection unit **12040**, and output a control command to the drive

system control unit **12010**. For example, the microcomputer **12051** can perform cooperative control for the purpose of realizing functions of an advanced driver assistance system (ADAS) including vehicle collision avoidance, impact mitigation, following traveling based on an inter-vehicle distance, vehicle speed maintenance driving, vehicle collision warning, vehicle lane deviation warning, and the like.

[0229] Further, by controlling the driving force generation device, the steering mechanism, the braking device, and the like on the basis of information regarding the vicinity of the vehicle acquired by the vehicle external information detection unit **12030** or the vehicle internal information detection unit **12040**, the microcomputer **12051** can perform cooperative control for the purpose of automated driving or the like in which autonomous travel is performed without depending on an operation of the driver.

[0230] In addition, the microcomputer **12051** can output a control command to the body system control unit **12020** on the basis of the information outside the vehicle acquired by the vehicle external information detection unit **12030**. For example, the microcomputer **12051** can perform cooperative control for the purpose of controlling headlamps in accordance with a position of a preceding vehicle or an oncoming vehicle detected by the vehicle external information detection unit **12030** and achieving antiglare by switching a high beam to a low beam, or the like.

[0231] The sound image output unit **12052** transmits an output signal of at least one of audio and an image to an output device capable of visually or audibly notifying an occupant of a vehicle or the outside of the vehicle of information. In the example of FIG. 26, an audio speaker **12061**, a display unit **12062**, and an instrument panel **12063** are illustrated as output devices. The display unit **12062** may include, for example, at least one of an onboard display and a head-up display.

[0232] FIG. 27 is a diagram showing an example of an installation position of the imaging unit **12031**.

[0233] In FIG. 27, a vehicle **12100** includes imaging units **12101**, **12102**, **12103**, **12104**, and **12105** as the imaging unit **12031**.

[0234] The imaging units **12101**, **12102**, **12103**, **12104**, and **12105** are provided at positions such as a front nose, side-view mirrors, a rear bumper, a back door, and an upper portion of a windshield in a vehicle interior of the vehicle **12100**, for example. The imaging unit **12101** provided on the front nose and the imaging unit **12105** provided in the upper portion of the windshield in the vehicle interior mainly acquire images in front of the vehicle **12100**. The imaging units **12102** and **12103** provided on the side mirrors mainly acquire images on a lateral side of the vehicle **12100**. The imaging unit **12104** provided on the rear bumper or the back door mainly acquires images behind the vehicle **12100**. Front view images acquired by the imaging units **12101** and **12105** are mainly used for detection of preceding vehicles, pedestrians, obstacles, traffic signals, traffic signs, lanes, and the like.

[0235] Also, FIG. 27 shows an example of imaging ranges of the imaging units **12101** to **12104**. An imaging range **12111** indicates an imaging range of the imaging unit **12101** provided at the front nose, imaging ranges **12112** and **12113** respectively indicate imaging ranges of the imaging units **12102** and **12103** provided at the side mirrors, and an imaging range **12114** indicates an imaging range of the imaging unit **12104** provided at the rear bumper or the back door. For example, a bird's-eye view image of the vehicle **12100** as viewed from above can be obtained by superimposing image data captured by the imaging units **12101** to **12104**.

[0236] At least one of the imaging units **12101** to **12104** may have a function of acquiring distance information. For example, at least one of the imaging units **12101** to **12104** may be a stereo camera configured of a plurality of imaging elements or may be an imaging element having pixels for phase difference detection.

[0237] For example, by obtaining distances to each three-dimensional object within the imaging range **12111** to **12114** and changes of the distances over time (relative velocity with respect to the vehicle **12100**) on the basis of distance information obtained from the imaging units **12101** to

12104, the microcomputer **12051** can extract, particularly, the closest three-dimensional object on a traveling path of the vehicle **12100**, which is a three-dimensional object traveling at a predetermined speed (for example, 0 km/h or higher) in the substantially same direction as the vehicle **12100**, as a preceding vehicle. Further, the microcomputer **12051** can set an inter-vehicle distance to be secured in advance from the preceding vehicle and can perform automated braking control (also including following stop control) or automated acceleration control (also including following start control). In this way, it is possible to perform cooperative control for the purpose of automated driving or the like in which autonomous travel is performed without depending on an operation of the driver.

[0238] For example, the microcomputer **12051** can classify and extract three-dimensional object data regarding three-dimensional objects into two-wheeled vehicles, ordinary vehicles, large vehicles, pedestrians, and other three-dimensional objects such as utility poles on the basis of the distance information obtained from the imaging units **12101** to **12104** and use the three-dimensional object data for automatic avoidance of obstacles. For example, the microcomputer **12051** identifies obstacles in the vicinity of the vehicle **12100** into obstacles that can be visually recognized by the driver of the vehicle **12100** and obstacles that are difficult to be visually recognized. In addition, the microcomputer **12051** determines a collision risk indicating a degree of risk of collision with each obstacle, and when the collision risk is equal to or greater than a set value and there is a possibility of collision, outputs a warning to the driver via the audio speaker **12061** or the display unit **12062** and performs forced deceleration or avoidance steering via the drive system control unit **12010**, so that it can perform driving assistance for collision avoidance.

[0239] At least one of the imaging units **12101** to **12104** may be an infrared camera that detects infrared light. For example, the microcomputer **12051** can recognize a pedestrian by determining whether or not a pedestrian is present in captured images of the imaging units **12101** to **12104**. Such recognition of a pedestrian is performed through, for example, a procedure of extracting feature points in the captured images of the imaging units **12101** to **12104** serving as infrared cameras, and a procedure of performing pattern matching processing on a series of feature points indicating a contour of an object to determine whether or not the object is a pedestrian. When the microcomputer **12051** determines that a pedestrian is present in the captured images of the imaging units **12101** to **12104** and recognizes the pedestrian, the sound image output unit **12052** controls the display unit **12062** such that a square contour line for emphasis is superimposed on the recognized pedestrian and is displayed. In addition, the sound image output unit **12052** may control the display unit **12062** so that an icon or the like indicating a pedestrian is displayed at a desired position.

[0240] An example of the vehicle control system to which the technique according to the present disclosure may be applied has been described above. The technique according to the present disclosure may be applied to the imaging unit **12031** and the like among the above-described configurations. Specifically, any one or more of the above-mentioned imaging devices **100**, **100A**, **100B**, **100C**, **100D**, **100E**, **100F**, **100G**, and **100H** can be applied to the imaging unit **12031**. By applying the technique according to the present disclosure to the imaging unit **12031**, a clearer captured image can be obtained, and thus it is possible to reduce a driver's fatigue.

In addition, the present disclosure can also adopt the following configurations.

[0241] (1) An imaging device including: [0242] a semiconductor substrate including a plurality of photoelectric conversion elements; [0243] a plurality of color filters that are provided on the semiconductor substrate and face each of the plurality of photoelectric conversion elements; and [0244] a partition wall that is provided on the semiconductor substrate and provides separation between one color filter and another color filter adjacent to each other among the plurality of color filters, [0245] wherein the partition wall includes a first metal layer, [0246] a first translucent partition wall layer that covers a side surface of the first metal layer, and [0247] a second translucent partition wall layer located between the first metal layer and the first partition wall layer, and [0248] a refractive index of the second partition wall layer is larger than a refractive

index of the first partition wall layer.

[0249] (2) The imaging device according to the above (1), wherein refractive indexes of the color filters are larger than the refractive index of the first partition wall layer.

[0250] (3) The imaging device according to the above (1) or (2) further including a lens disposed on a side opposite to the semiconductor substrate with the color filters interposed therebetween, [0251] wherein the first metal layer includes an end surface located on the lens side, [0252] the second partition wall layer covers the end surface of the first metal layer, and [0253] the first partition wall layer covers the end surface via the second partition wall layer.

[0254] (4) The imaging device according to any one of the above (1) to (3), wherein the second partition wall layer, the first partition wall layer, and the color filters are laminated in order on the photoelectric conversion elements.

[0255] (5) The imaging device according to any one of the above (1) to (4) further including a light-shielding film disposed between the partition wall and the semiconductor substrate.

[0256] (6) The imaging device according to the above (5), wherein the light-shielding film is made of a metal.

[0257] (7) The imaging device according to any one of the above (1) to (6), [0258] wherein the side surface of the first metal layer includes [0259] a first side surface, and [0260] a second side surface located on a side opposite to the first side surface, and in the second partition wall layer, [0261] a thickness of a portion that covers the first side surface and a thickness of a portion that covers the second side surface are different from each other.

[0262] (8) The imaging device according to any one of the above (1) to (7), wherein a width of the one color filter and a width of another color filter are different from each other.

[0263] (9) The imaging device according to any one of the above (1) to (8), [0264] wherein the semiconductor substrate further includes an element separation layer that separates one photoelectric conversion element from another photoelectric conversion element, which are adjacent to each other among the plurality of photoelectric conversion elements, [0265] the partition wall is located on the element separation layer, and [0266] an amount of shift of the partition wall toward a central region of an imaging region including the plurality of photoelectric conversion elements with respect to the element separation layer increases toward a side further separated from the central region.

[0267] (10) The imaging device according to any one of the above (1) to (8), [0268] wherein the semiconductor substrate further includes an element separation layer that separates one photoelectric conversion element from another photoelectric conversion element, which are adjacent to each other among the plurality of photoelectric conversion elements, [0269] the partition wall is located on the element separation layer, and [0270] the element separation layer includes [0271] a second metal layer, and [0272] an insulating layer that covers a side surface of the second metal layer.

[0273] (11) The imaging device according to the above (10), wherein the first metal layer and the second metal layer are integrated with each other.

[0274] (12) The imaging device according to the above (10) further including a metal light-shielding film disposed between the first metal layer and the second metal layer, [0275] wherein the second metal layer and the metal light-shielding film are integrated with each other.

[0276] (13) The imaging device according to any one of the above (1) to (12), [0277] wherein the second partition wall layer is configured of a silicon carbide film having an amorphous crystal structure, and [0278] the first partition wall layer is configured of a silicon oxide film.

[0279] (14) An electronic device including: [0280] an optical component; [0281] an imaging device on which light transmitted through the optical component is incident; [0282] and [0283] a signal processing circuit configured to process a signal output from the imaging device, [0284] wherein the imaging device includes: [0285] a semiconductor substrate including a plurality of photoelectric conversion elements; [0286] a plurality of color filters that are provided on the semiconductor

substrate and face each of the plurality of photoelectric conversion elements; and [0287] a partition wall that is provided on the semiconductor substrate and provides separation between one color filter and another color filter adjacent to each other among the plurality of color filters, [0288] the partition wall includes [0289] a first metal layer, [0290] a first translucent partition wall layer that covers a side surface of the first metal layer, and [0291] a second translucent partition wall layer located between the first metal layer and the first partition wall layer, and [0292] a refractive index of the second partition wall layer is larger than a refractive index of the first partition wall layer.

REFERENCE SIGNS LIST

[0293] **2** Partition wall [0294] **11, 31** Insulating film [0295] **20** First metal layer [0296] **20', 50'** Metal layer [0297] **20a** First side surface [0298] **20b** Second side surface [0299] **20c** Upper end surface [0300] **21** First partition wall layer [0301] **21', 22', 51', 52'** Insulating layer [0302] **22** Second partition wall layer [0303] **30** Metal light-shielding film [0304] **30'** Metal film [0305] **50** Second metal layer [0306] **51** First insulating layer [0307] **52** Second insulating layer [0308] **100, 100A, 100B, 100C, 100D, 100E, 100F, 100G, 100H** Imaging device [0309] **102** Pixel [0310] **103** Pixel region [0311] **104** Vertical drive circuit [0312] **105** Column signal processing circuit [0313] **106** Horizontal drive circuit [0314] **107** Output circuit [0315] **108** Control circuit [0316] **109** Vertical signal line [0317] **110** Horizontal signal line [0318] **111** Semiconductor substrate [0319] **201** Solid-state imaging device [0320] **210** Optical lens [0321] **211** Shutter device [0322] **212** Drive circuit [0323] **213** Signal processing circuit [0324] **300** Electronic device [0325] **10402** Imaging unit [0326] **11000** Endoscopic operation system [0327] **11100** Endoscope [0328] **11101** Lens barrel [0329] **11102** Camera head [0330] **11110** Surgical instrument [0331] **11111** Pneumoperitoneum tube [0332] **11112** Energized treatment tool [0333] **11120** Support arm device [0334] **11131** Operator (doctor) [0335] **11131** Operator [0336] **11132** Patient [0337] **11133** Patient bed [0338] **11200** Cart [0339] **11201** Camera control unit [0340] **11202** Display device [0341] **11203** Light source device [0342] **11204** Input device [0343] **11205** Treatment tool control device [0344] **11206** Pneumoperitoneum device [0345] **11207** Recorder [0346] **11208** Printer [0347] **11400** Transmission cable [0348] **11401** Lens unit [0349] **11402** Imaging unit [0350] **11403** Driving unit [0351] **11404** Communication unit [0352] **11405** Camera head control unit [0353] **11411** Communication unit [0354] **11412** Image processing unit [0355] **11413** Control unit [0356] **12000** Vehicle control system [0357] **12001** Communication network [0358] **12010** Drive system control unit [0359] **12020** Body system control unit [0360] **12030** Vehicle external information detection unit [0361] **12031** Imaging unit [0362] **12040** Vehicle internal information detection unit [0363] **12041** Driver state detection unit [0364] **12050** Integrated control unit [0365] **12051** Microcomputer [0366] **12052** Sound image output unit [0367] **12061** Audio speaker [0368] **12062** Display unit [0369] **12063** Instrument panel [0370] **12100** Vehicle [0371] **12101** to **12105** Imaging unit [0372] **12111** to **12114** Imaging range [0373] **AMP** Amplifying transistor [0374] **AR1** Central region [0375] **AR2** Peripheral region [0376] **C20** Central position [0377] **CCU** **11201** Imaging unit [0378] **CF, CF1, CF2, CF3, CF4** Color filter [0379] **CRP5** Central position [0380] **FD** Floating diffusion [0381] **H** Trench [0382] **I** In-vehicle network [0383] **ICG** Indocyanine green [0384] **L1, L2, L3, L4, L11, L12, L13** Light [0385] **L21** Light [0386] **ML** Micro lens [0387] **MLE** End portion [0388] **n21, n22, ncf** Refractive index [0389] **PD, PD1, PD2, PD3, PD4** Photodiode [0390] **PU** Pixel unit [0391] **QE** Quantum efficiency [0392] **RP1, RP2, RP3, RP4, RP5, RP6, RP7, RP8, RP9, RP10, RP11** Resist pattern [0393] **RST** Reset transistor [0394] **SEL** Selection transistor [0395] **SiO2** Silicon oxide film [0396] **TR** Transfer transistor [0397] **VDD** Power line [0398] **W20, W30, WCFB, WCFE, WCFG, WCFR, WRP5** Width [0399] **Wgap** Distance (shift amount) [0400] **θ1, θ2, θ3** Incidence angle

Claims

- 1.** A light detecting device, comprising: a semiconductor substrate comprising: a first surface configured to receive light; and a second surface opposite to the first surface; a first photoelectric conversion region in the semiconductor substrate; a second photoelectric conversion region in the semiconductor substrate and adjacent to the first photoelectric conversion region; a first color filter above the first photoelectric conversion region in a cross-sectional view; a second color filter above the second photoelectric conversion region in the cross-sectional view; and a separation region between the first color filter and the second color filter in the cross-sectional view, wherein the separation region includes a first film, a second film, and a first metal film, the first film is between the first color filter and the second film in the cross-sectional view, the second film is between the first film and the first metal film in the cross-sectional view, a refractive index of the first film is less than a refractive index of the first color filter, and the refractive index of the first film is less than a refractive index of the second film.
 - 2.** The light detecting device according to claim 1, wherein the separation region further includes a third film, and the third film includes silicon oxide.
 - 3.** The light detecting device according to claim 2, further comprising a second metal film, wherein the second metal film includes a metal, the second metal film is covered by the third film, and the third film is between the second film and the second metal film in the cross-sectional view.
 - 4.** The light detecting device according to claim 1, wherein the first film includes silicon.
 - 5.** The light detecting device according to claim 1, wherein the first film includes oxide.
 - 6.** The light detecting device according to claim 1, wherein the second film includes silicon carbide and has an amorphous crystal structure.
 - 7.** The light detecting device according to claim 1, wherein the second film is below the first film in the cross-sectional view.
 - 8.** The light detecting device according to claim 1, further comprising a lens on a side opposite to the semiconductor substrate, wherein an end surface of the first metal film is on a side of the lens, and the second film covers the end surface of the first metal film.
 - 9.** The light detecting device according to claim 1, wherein the first metal film includes a first side surface and a second side surface on a side opposite to the first side surface, a first portion of the second film covers the first side surface of the first metal film, a second portion of the second film covers the second side surface of the first metal film, and a thickness of the first portion is different from a thickness of the second portion.
 - 10.** The light detecting device according to claim 1, wherein a width of the first color filter is different from a width of the second color filter.
 - 11.** The light detecting device according to claim 1, wherein the semiconductor substrate further includes an element separation layer that separates the first photoelectric conversion region from the second photoelectric conversion region which is adjacent to the first photoelectric conversion region, the separation region is on the element separation layer, and the element separation layer includes a third metal film, and an insulating film that covers a side surface of the third metal film.
 - 12.** The light detecting device according to claim 11, wherein the first metal film is integrated with the third metal film.
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